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NATURE OF CONVEYANCE:	Notice of License Agreement		
CONVEYING PARTY DATA			
Name	Formerly	Execution Date	Entity Type
SunEdison Semiconductor Limited	FORMERLY SunEdison Semiconductor Pte. Ltd.	05/27/2014	Limited Company: SINGAPORE
RECEIVING PARTY DATA			
Name:	SunEdison Semiconductor Technology Pte. Ltd.		
Street Address:	501 Pearl Drive (City of O#Fallon)		
Internal Address:	c/o SunEdison Semiconductor, LLC		
City:	St. Peters		
State/Country:	MISSOURI		
Postal Code:	63376		
Entity Type:	Private Limited Company: SINGAPORE		
PROPERTY NUMBERS Total: 8			
Property Type	Number	Word Mark	
Registration Number:	3116254	ADVANTA	
Registration Number:	2400584	MAGIC DENUDED ZONE	
Registration Number:	2459810	MDZ	
Registration Number:	2506929	MEMC	
Registration Number:	3216953	OPTIA	
Registration Number:	3231772	PERFECT SILICON	
Registration Number:	3325895	PERFECTSOI	
Registration Number:	2526106	TECHNOLOGY IS BUILT ON US	
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DATE SIGNED:	06/05/2014

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By: Sally H. Townsley
Name: Sally H. Townsley
Title:

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**Schedule A
Patents**

City	App Number	Pub Number	Title	Patent Number
CN	200580048849.5	101133193	CONTROLLING MELT-SOLID INTERFACE SHAPE OF A GROWING SILICON CRYSTAL USING A VARIABLE MAGNETIC FIELD	ZL200580048849.5
CN	200910265726.7	101724903A	A MELTER ASSEMBLY AND METHOD FOR CHARGING A CRYSTAL FORMING APPARATUS WITH MOLTEN SOURCE MATERIAL	ZL200910265726.7
CN	200580048843.8	101133192	ELECTROMAGNETIC PUMPING OF LIQUID SILICON IN A CRYSTAL GROWING PROCESS	ZL200580048843.8
CN	201310072159.X	CN 103147122A	CONTROLLING AGGLOMERATED POINT DEFECT AND OXYGEN CLUSTER FORMATION INDUCED BY THE LATERAL SURFACE OF A SILICON SINGLE CRYSTAL DURING CZ GROWTH	
CN	200780027056.4	CN101490314A	CONTROLLING AGGLOMERATED POINT DEFECT AND OXYGEN CLUSTER FORMATION INDUCED BY THE LATERAL SURFACE OF A SILICON SINGLE CRYSTAL DURING CZ GROWTH	ZL200780027056.4
CN	200780011609.7	CN101410224A	DOUBLE SIDE WAFER GRINDER AND METHODS FOR ASSESSING WORKPIECE NANOTOPOLOGY	ZL200780011609.7
CN	200780011360.X	CN 101410977A	SEMICONDUCTOR WAFER WITH HIGH THERMAL CONDUCTIVITY	
CN	200780024440.9	CN101479840A	WAFER PLATFORM	ZL200780024440.9
CN	200980111773.4	CN101981664A	METHODS FOR ETCHING THE EDGE OF A SILICON WAFER	
CN	201180058948.7	CN 103250234A	PROCESS FOR ANNEALING SEMICONDUCTOR WAFERS WITH FLAT DOPANT DEPTH PROFILES	
CN	200880020775.8	CN 101772836A	SUSCEPTOR FOR IMPROVING THROUGHPUT AND REDUCING WAFER DAMAGE	ZL200880020775.8
CN	200880122656.3	CN101910475A	EPITAXIAL BARREL SUSCEPTOR HAVING IMPROVED THICKNESS UNIFORMITY	1418650
CN	200880122697.2	CN 102105620A	SUSCEPTOR WITH SUPPORT BOSSES	ZL200880122697.2

Ctry	App Number	Pub Number	Title	Patent Number
CN	200980125319.4	CN 102076890A	CONTROLLING A MELT-SOLID INTERFACE SHAPE OF A GROWING SILICON CRYSTAL USING AN UNBALANCED MAGNETIC FIELD AND ISO-ROTATION	
CN	200980129655.6	CN 102112665A	GENERATING A PUMPING FORCE IN A SILICON MELT BY APPLYING A TIME-VARYING MAGNETIC FIELD	ZL200980129655.6
CN	201080059531.8	CN 102687237A	METHODS FOR PROCESSING SILICON ON INSULATOR WAFERS	
CN	201080064913.X	103026460	METHOD FOR THE PREPARATION OF A MULTI-LAYERED CRYSTALLINE STRUCTURE	
CN	201080058166.9	102668054	METHODS FOR ANALYSIS OF WATER AND SUBSTRATES RINSED IN WATER	
CN	201080058077.4	CN 102687260A	METHODS FOR MONITORING THE AMOUNT OF CONTAMINATION IMPARTED INTO SEMICONDUCTOR WAFERS DURING WAFER PROCESSING	
CN	201080058651.6	102687262	SEMICONDUCTOR WAFER TRANSPORT SYSTEM	
CN	201180010887.7	102770955	METHODS FOR REDUCING THE WIDTH OF THE UNBONDED REGION IN SOI STRUCTURES AND WAFERS AND SOI STRUCTURES PRODUCED BY SUCH METHODS	
CN	201180037419.9	103053019	SEMICONDUCTOR AND SOLAR WAFERS	
CN	201180037452.1	103038875	SEMICONDUCTOR AND SOLAR WAFERS AND METHOD FOR PROCESSING SAME	
CN	201180016139.X	102844151	HYDROSTATIC PAD PRESSURE MODULATION IN A SIMULTANEOUS DOUBLE SIDE WAFER GRINDER	
CN	201180032826.0	102959697	METHODS FOR IN-SITU PASSIVATION OF SILICON-ON-INSULATOR WAFERS	
CN	201180022194.X	CN 102870206A	WAFER SUPPORT RING	
CN	201180046144.5	CN103125011A	ADAPTER RING FOR SILICON ELECTRODE	

City	App Number	Pub Number	Title	Patent Number
CN	02828722.3	CN 1625802A	PROCESS FOR CONTROLLING DENUDED ZONE DEPTH IN AN IDEAL OXYGEN PRECIPITATING SILICON WAFER	ZL02828722.3
CN	2004800256648.9	CN 1846017A	PROCESS FOR PREPARING A STABILIZED IDEAL OXYGEN PRECIPITATING SILICON WAFER	ZL2004800256648
CN	200380108637.2	CN1738931A	PROCESS FOR PREPARING SINGLE CRYSTAL SILICON USING CRUCIBLE ROTATION TO CONTROL TEMPERATURE GRADIENT	ZL200380108637
CN	98809399.5	1271463	LOW DEFECT DENSITY, SELF-INTERSTITIAL DOMINATED SILICON	ZL98809399.5
CN	01815935.4	CN 1461360A	NITROGEN-DOPED SILICON SUBSTANTIALLY FREE OF OXIDATION INDUCED STACKING FAULTS	ZL01815935.4
CN	02805098.3	1500159	LOW DEFECT DENSITY SILICON SUBSTANTIALLY FREE OF OXIDATION INDUCED STACKING FAULTS HAVING A VACANCY-DOMINATED CORE IDEAL OXYGEN PRECIPITATING SILICON WAFERS WITH	ZL02805098.3
CN	02825681.6	CN 1606799A	NITROGEN/CARBON STABILIZED OXYGEN PRECIPITATE NUCLEATION CENTERS AND PROCESS FOR MAKING THE SAME	ZL02825681.6
CN	02822314.4	1585838	INTERMITTENT FEEDING TECHNIQUE FOR INCREASING THE MELTING RATE OF POLYCRYSTALLINE SILICON	ZL02822314.4
CN	200710086008.4	101054717	INTERMITTENT FEEDING TECHNIQUE FOR INCREASING THE MELTING RATE OF POLYCRYSTALLINE SILICON	200710086008
CN	02814507.0	CN 1533599A	PROCESS FOR PRODUCING SILICON ON INSULATOR STRUCTURE HAVING INTRINSIC GETTERING BY ION IMPLANTATION	ZL02814507.0
CN	200380108618X	CN 1738930A	A CRYSTAL PULLER AND METHOD FOR GROWING A MONOCRYSTALLINE INGOT	ZL200380108618X
CN	200580031949.7	CN 101031675A	PARTIALLY DEVITRIFIED CRUCIBLE	ZL200580031949.7
CN	200580022823.3	CN 1981369 A	PROCESS FOR METALLIC CONTAMINATION REDUCTION IN SILICON WAFERS	ZL200580022823.3
CN	200580027650.4	CN 101006008A	SYSTEMS AND METHODS FOR MANUFACTURING GRANULAR MATERIAL, AND FOR MEASURING AND REDUCING DUST IN GRANULAR MATERIAL	ZL200580027650.4

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CN	200580028099.5	CN 101006205A	A MELTER ASSEMBLY AND METHOD FOR CHARGING A CRYSTAL FORMING APPARATUS WITH MOLTEN SOURCE MATERIAL	ZL 200580028099.5
CN	200580008470.1	CN 1933940A	WAFER CLAMPING DEVICE FOR A DOUBLE SIDE GRINDER	ZL 200580008470.1
CN	200580032316.8	CN 101027267A	METHOD FOR PURIFYING SILICON CARBIDE COATED STRUCTURES	ZL 200580032316.8
CN	95193037.0	1147782	SEMICONDUCTOR WAFER POLISHING APPARATUS AND METHOD	95193037.0
CN	96102289.2	1149634	SURFACE-TREATED CRUCIBLES FOR IMPROVED ZERO DISLOCATION PERFORMANCE	ZL 96102289.2
CN	96111030.9	1152037	METHODS FOR IMPROVING ZERO DISLOCATION YIELD OF SINGLE CRYSTALS	ZL 96111030.9
CN	96107584.8	1147570	METHOD FOR CONTROLLING GROWTH OF A SILICON CRYSTAL	96107584.8
CN	96110663.8	1147032	METHOD FOR PREPARING MOLTEN SILICON MELT FROM POLYCRYSTALLINE SILICON CHARGE	96110663.8
CN	96100507.6	1136604	PRECISION CONTROLLED PRECIPITATION OF OXYGEN IN SILICON	96100507.6
CN	97122810.8	1188821	PROCESS AND APPARATUS FOR CONTROLLING THE OXYGEN CONTENT IN SILICON WAFERS HEAVILY DOPED WITH ANTIMONY OR ARSENIC	97122810.8
CN	98803695.9	1251206	IDEAL OXYGEN PRECIPITATING SILICON WAFERS AND OXYGEN OUT-DIFFUSION-LESS PROCESS THEREFOR	ZL 98803695.9
CN	98806904.0	1261928	LOW DEFECT DENSITY SINGLE CRYSTAL SILICON	ZL 98806904.0
CN	200710089120.3	CN 101070621A	LOW DEFECT DENSITY, IDEAL OXYGEN PRECIPITATING SILICON	200710089120
CN	98805223.7	1256723	LOW DEFECT DENSITY, IDEAL OXYGEN PRECIPITATING SILICON	ZL 98805223.7

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CN	200610058336.9	CN1854353A	LOW DEFECT DENSITY, SELF-INTERSTITIAL DOMINATED SILICON	ZL200610058336.9
CN	98805271.7	1257556	LOW DEFECT DENSITY, SELF-INTERSTITIAL DOMINATED SILICON	ZL98805271.7
CN	200610139268.9	CN 1936112A	LOW DEFECT DENSITY SILICON	ZL200610139268.9
CN	98810175.0	1276026	PROCESS FOR PREPARING A SILICON MELT FROM A POLYSILICON CHARGE	ZL98810175.0
CN	99807420.9	1305540	PROCESS AND APPARATUS FOR PREPARATION OF SILICON CRYSTALS WITH REDUCED METAL CONTENT	ZL 99807420.9
CN	99800258.5	1256724	CRUCIBLE AND METHOD OF PREPARATION THEREOF	ZL 99800258.5
CN	99810628.3	CN 1317149A	NON-UNIFORM MINORITY CARRIER LIFETIME DISTRIBUTIONS IN HIGH PERFORMANCE SILICON POWER DEVICES	ZL99810628.3
CN	99806946.9	CN 1307653A	EPIAXIAL SILICON WAFERS SUBSTANTIALLY FREE OF GROWN-IN DEFECTS	ZL99806946.9
CN	99811816.8	1322260	CONTINUOUS OXIDATION PROCESS FOR CRYSTAL PULLING APPARATUS	ZL99811816.8
CN	200610139269.3	CN 1936113A	LOW DEFECT DENSITY, VACANCY DOMINATED SILICON	ZL200610139269.3
CN	98805003.X	1255169	LOW DEFECT DENSITY, VACANCY DOMINATED SILICON	ZL98805003.X
CN	99812088.X	1323362	THERMALLY ANNEALED, LOW DEFECT DENSITY SINGLE CRYSTAL SILICON	ZL99812088.X
CN	99810605.4	1321334	THERMALLY ANNEALED WAFERS HAVING IMPROVED INTERNAL GETTERING AND PROCESS FOR THE PREPARATION THEREOF	ZL99810605.4
CN	99811709.9	CN 1321336A	SILICON ON INSULATOR STRUCTURE FROM LOW DEFECT DENSITY SINGLE CRYSTAL SILICON	ZL99811709.9

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CN	99810607.0	1319253	NON-OXYGEN PRECIPITATING CZOCHRALSKI SILICON WAFERS	ZL99810607.0
CN	99810597.X	1317152	IDEAL OXYGEN PRECIPITATING SILICON WAFERS AND OXYGEN OUT-DIFFUSION-LESS PROCESS THEREFOR	ZL99810597.X
CN	00804241.1	1341168	HEAT SHIELD ASSEMBLY FOR CRYSTAL PULLER	ZL00804241.1
CN	01812067.9	1440566	METHOD AND APPARATUS FOR FORMING AN EPITAXIAL SILICON WAFER WITH A DENUDED ZONE	ZL 01812067.9
CN	99807092.0	1304459	PROCESS FOR GROWTH OF DEFECT FREE SILICON CRYSTALS OF ARBITRARILY LARGE DIAMETERS AT ARBITRARY GROWTH RATES MAXIMUM THROUGHOUT	ZL99807092.0
CN	01818359.X	1473214	METHOD FOR THE PRODUCTION OF LOW DEFECT DENSITY SILICON	ZL01818359.X
CN	00805045.7	1343264	STRONTIUM DOPING OF MOLTEN SILICON FOR USE IN CRYSTAL GROWING PROCESS	ZL00805045.7
CN	00805047.3	1343265	BARIUM DOPING OF MOLTEN SILICON FOR USE IN CRYSTAL GROWING PROCESS	ZL00805047.3
CN	01818313.1	1473213	PROCESS FOR PREPARING LOW DEFECT DENSITY SILICON USING HIGH GROWTH RATES	ZL01818313.1
CN	01810809.1	1434884	MODIFIED SUSCEPTOR FOR USE IN CHEMICAL VAPOR DEPOSITION PROCESS	ZL01810809.1
CN	01810808.3	CN 1434883A	EPITAXIAL SILICON WAFER FREE FROM AUTODOPING AND BACKSIDE HALO	ZL01810808.3
DE	01905374.3	1257697	PROCESS FOR PRODUCING A SILICON MELT	1257697
DE	05107781.6	1669478	NITROGEN-DOPED SILICON SUBSTANTIALLY FREE OF OXIDATION INDUCED STACKING FAULTS	60141611.2-08
DE	10177865.2	2295619	LOW DEFECT DENSITY SILICON HAVING A VACANCY-DOMINATED CORE SUBSTANTIALLY FREE OF OXIDATION INDUCED STACKING FAULTS	

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DE	02789582.0	1448517	INTERMITTENT FEEDING TECHNIQUE FOR INCREASING THE MELTING RATE OF POLYCRYSTALLINE SILICON	60220939
DE	02773835.0	1493179	PROCESS FOR CONTROLLING DENUDED ZONE DEPTH IN AN IDEAL OXYGEN PRECIPITATING SILICON WAFER	60224099.9-08
DE	10152849.5	2177648	PROCESS FOR PREPARING SINGLE CRYSTAL SILICON USING CRUCIBLE ROTATION TO CONTROL TEMPERATURE GRADIENT	2177648
DE	05772987.3	1781843	PARTIALLY DEVITRIFIED CRUCIBLE	602005034557.4
DE	05739906.5	1743364	PROCESS FOR METALLIC CONTAMINATION REDUCTION IN SILICON WAFERS	602005031873.9
DE	10179629.0	2269291	PROCESS FOR METALLIC CONTAMINATION REDUCTION IN SILICON WAFERS	602005033224
DE	5852293.9	1831436	CONTROLLING MELT-SOLID INTERFACE SHAPE OF A GROWING SILICON CRYSTAL USING A VARIABLE MAGNETIC FIELD	1831436
DE	05788988.3	1756337	MELTER ASSEMBLY AND METHOD FOR CHARGING A CRYSTAL PULLER WITH MOLTEN SOURCE MATERIAL	602005014103.0-08
DE	5852345.7	1848844	ELETROMAGNETIC PUMPING OF LIQUID SILICON IN A CRYSTAL GROWING PROCESS	1848844
DE	05711676.6	1735127	WAFER CLAMPING DEVICE FOR A DOUBLE SIDE GRINDER	602005040622.0-08
DE	10157117.2	2199267	METHOD FOR PURIFYING SILICON CARBIDE STRUCTURES	2199267
DE	07797092.9	1981685	DOUBLE SIDE WAFER GRINDER AND METHODS FOR ASSESSING WORKPIECE NANOTOPOLOGY	602007023020.9
DE	08848771.5	2215290	REDUCTION OF AIR POCKETS IN SILICON CRYSTALS BY AVOIDING THE INTRODUCTION OF NEARLY-INSOLUBLE GASES INTO THE MELT	602008012534.3-08
DE	09727521.8	2260507	METHODS FOR ETCHING THE EDGE OF A SILICON WAFER	602009010023.8-08

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DE	08771365.7	2165358	SUSCEPTOR FOR IMPROVING THROUGHPUT AND REDUCING WAFER DAMAGE	602008008977.0-08
DE	08866204.4	2222901	EPITAXIAL BARREL SUSCEPTOR HAVING IMPROVED THICKNESS UNIFORMITY	602008010676.4-08
DE	8869803	2225070	NANOTOPOGRAPHY CONTROL AND OPTIMIZATION USING FEEDBACK FROM WARP DATA	602008030309.8-08
DE	09791617.5	2321617	METHOD AND DEVICE FOR CONTINUOUSLY MEASURING SILICON ISLAND ELEVATION	602009015620.9
DE	09774069.0	2311080	LOW THERMAL MASS SEMICONDUCTOR WAFER SUPPORT	602009013724.7-08
DE	09791232.3	2321450	GENERATING A PUMPING FORCE IN A SILICON MELT BY APPLYING A TIME-VARYING MAGNETIC FIELD	602009010251.6-08
DE	10713392.8	2414793	SYSTEMS AND METHODS FOR WEIGHING A PULLED OBJECT	2414793
DE	04756166.7	1641964	PROCESS FOR PREPARING A STABILIZED IDEAL OXYGEN PRECIPITATING SILICON WAFER	602004016851.3
DE	03779446.8	1560951	PROCESS FOR PREPARING SINGLE CRYSTAL SILICON USING CRUCIBLE ROTATION TO CONTROL TEMPERATURE GRADIENT	60334722.3-08
DE	05024867.3	1624482	THERMALLY ANNEALED WAFERS HAVING IMPROVED INTERNAL GETTERING	69941196.3-08
DE	10179080.6	2261958	PROCESS FOR MAKING NON-OXYGEN PRECIPITATING CZOCHRALSKI SILICON WAFERS	69944729.1-08
DE	07023865.4	1914796	METHOD OF FORMING NON-OXYGEN PRECIPITATING CZOCHRALSKI SILICON WAFERS	69944254.0-08
DE	1930582.0	1287187	MODIFIED SUSCEPTOR FOR USE IN CHEMICAL VAPOR DEPOSITION PROCESS	60139008.3-08
DE	01930651.3	1287188	EPITAXIAL SILICON WAFER FREE FROM AUTODOPING AND BACKSIDE HALO	60127252.8-08

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DE	02720794.3	1348048	PROCESS FOR PREPARING SINGLE CRYSTAL SILICON HAVING IMPROVED GATE OXIDE INTEGRITY	1348048
DE	01968299.6	1325178	NITROGEN-DOPED SILICON SUBSTANTIALLY FREE OF OXIDATION INDUCED STACKING FAULTS	60115078.2-0
DE	02714762.8	1356139	LOW DEFECT DENSITY SILICON SUBSTANTIALLY FREE OF OXIDATION INDUCED STACKING FAULTS HAVING A VACANCY-DOMINATED CORE	60213759.4-08
DE	37689900.7	1560950	A CRYSTAL PULLER AND METHOD FOR GROWING A MONOCRYSTALLINE INGOT	60323863.4-08
DE	05763307.5	1791799	METHOD FOR PURIFYING SILICON CARBIDE COATED STRUCTURES	602005024989.3-08
DE	96917044.0	0758941	SEMICONDUCTOR WAFER POLISHING APPARATUS AND METHOD	0758941
DE	96304342.7	0748885	SURFACE-TREATED CRUCIBLES FOR IMPROVED ZERO DISLOCATION PERFORMANCE	69615282.7
DE	96304341.9	0753605	METHODS FOR IMPROVING ZERO DISLOCATION YIELD OF SINGLE CRYSTALS	69609907.1
DE	96303047.3	0745830	METHOD FOR CONTROLLING GROWTH OF A SILICON CRYSTAL	0745830
DE	96304813.7	0756024	METHOD FOR PREPARING MOLTEN SILICON MELT FROM POLYCRYSTALLINE SILICON CHARGE	69609782.6
DE	96301616.7	0732431	PRECISION CONTROLLED PRECIPITATION OF OXYGEN IN SILICON	69630328.0-08
DE	96303755.1	0747511	APPARATUS FOR ROTATING A CRUCIBLE OF A CRYSTAL PULLING MACHINE	0747511
DE	98906703.8	1002335	IDEAL OXYGEN PRECIPITATING SILICON WAFERS AND OXYGEN OUT-DIFFUSION-LESS PROCESS THEREFOR	69817365.1-08
DE	2027280.3	1300879	IDEAL OXYGEN PRECIPITATING SILICON WAFERS AND OXYGEN OUT-DIFFUSION-LESS PROCESS THEREFOR	69840004.6-08

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DE	98918113.6	0973963	LOW DEFECT DENSITY SINGLE CRYSTAL SILICON	0973963
DE	01126017.1	1209258	LOW DEFECT DENSITY SINGLE CRYSTAL SILICON	69824647.0-08
DE	01130907.7	1209259	LOW DEFECT DENSITY, SELF-INTERSTITIAL DOMINATED SILICON	69840960.7-08
DE	98919752	0973964	LOW DEFECT DENSITY SINGLE CRYSTAL SILICON	0973964
DE	99930636.8	1090168	ELECTRICAL RESISTANCE HEATER AND METHOD FOR CRYSTAL GROWING APPARATUS	69902911.2-08
DE	98952124.0	1025288	PROCESS FOR PREPARING A SILICON MELT FROM A POLYSILICON CHARGE	69824877.5
DE	99927525.8	1090167	PROCESS AND APPARATUS FOR PREPARATION OF SILICON CRYSTALS WITH REDUCED METAL CONTENT	69901183.3-08
DE	98915335.1	0973962	LOW DEFECT DENSITY IDEAL OXYGEN PRECIPITATING SILICON	69806369.4
DE	01109372.1	1146150	LOW DEFECT DENSITY, IDEAL OXYGEN PRECIPITATING SILICON	69841714.3-08
DE	99903333.5	0972095	CRUCIBLE AND METHOD OF PREPARATION THEREOF	69901135.3
DE	99942012.8	1110236	NON-UNIFORM MINORITY CARRIER LIFETIME DISTRIBUTIONS IN HIGH PERFORMANCE SILICON POWER DEVICES	69933681.3-08
DE	99956661.7	1133590	EPITAXIAL SILICON WAFERS SUBSTANTIALLY FREE OF GROWN-IN DEFECTS	69913731.4-08
DE	98919749.6	0972094	LOW DEFECT DENSITY SINGLE CRYSTAL SILICON	69801903.2
DE	02021897.0	1273684	LOW DEFECT DENSITY, VACANCY DOMINATED SILICON	69831618.5

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DE	99956562.5	1125008	THERMALLY ANNEALED, LOW DEFECT DENSITY SINGLE CRYSTAL SILICON	69908965.4-08
DE	99942528.3	1129471	THERMALLY ANNEALED WAFERS HAVING IMPROVED INTERNAL GETTERING	69928434.1-08
DE	00957400.5	1218571	PROCESS FOR PREPARING SINGLE CRYSTAL SILICON HAVING UNIFORM THERMAL HISTORY	60005985.5-08
DE	99945173.5	1114441	METHOD OF FORMING NON-OXYGEN PRECIPITATING CZOCHRALSKI SILICON WAFERS	69937803.6-08
DE	99944006.8	1110240	PROCESS FOR PREPARING AN IDEAL OXYGEN PRECIPITATING SILICON WAFER	69933777.1
DE	99930652.5	1090166	PROCESS FOR GROWTH OF DEFECT FREE SILICON CRYSTALS OF ARBITRARILY LARGE DIAMETERS	69901115.9
DE	00910060.3	1159470	HEAT SHIELD ASSEMBLY FOR CRYSTAL PULLER	1159470
DE	99930653.3	1127175	PROCESS FOR GROWTH OF DEFECT FREE SILICON CRYSTALS OF ARBITRARILY LARGE DIAMETERS AT ARBITRARY GROWTH RATES MAXIMUM THROUGHOUT	69902555.9-08
DE	01991951.3	1330562	METHOD FOR THE PRODUCTION OF LOW DEFECT DENSITY SILICON	60111071.4-08
DE	01273548.6	1337697	METHOD FOR PREPARING MOLTEN SILICON MELT FROM POLYCRYSTALLINE SILICON CHARGE	60115951.9-08
DE	00916304.9	1169496	STRONTIUM DOPING OF MOLTEN SILICON FOR USE IN CRYSTAL GROWING PROCESS	1169496
DE	00914953.5	1175519	BARIUM DOPING OF MOLTEN SILICON FOR USE IN CRYSTAL GROWING PROCESS	1175519
DE	915791.8	1171652	METHOD AND SYSTEM FOR CONTROLLING DIAMETER OF A SILICON CRYSTAL IN A LOCKED SEED LIFT GROWTH PROCESS	1171652
DE	01107427.5	1118697	LOW DEFECT DENSITY, VACANCY DOMINATED SILICON	69813041.3

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DE	00961957.8	1222325	METHOD FOR PRODUCING CZOCHRALSKI SILICON FREE OF AGGLOMERATED SELF-INTERSTITIAL DEFECTS	60019780T2
DE	00963572.3	1222324	PROCESS FOR SUPPRESSING THE NUCLEATION AND/OR GROWTH OF INTERSTITIAL TYPE DEFECTS BY CONTROLLING THE COOLING RATE THROUGH NUCLEATION	60010496.6-08
DE	01273046.1	1332246	PROCESS FOR PREPARING LOW DEFECT DENSITY SILICON USING HIGH GROWTH RATES	60106074.1-08
EP	10177965.2	2296619	LOW DEFECT DENSITY SILICON HAVING A VACANCY-DOMINATED CORE SUBSTANTIALLY FREE OF OXIDATION INDUCED STACKING FAULTS	
EP	10152849.5	2177648	PROCESS FOR PREPARING SINGLE CRYSTAL SILICON USING CRUCIBLE ROTATION TO CONTROL TEMPERATURE GRADIENT	2177648
EP	10178951.9	2266923	SYSTEMS AND METHODS FOR MANUFACTURING GRANULAR MATERIAL, AND FOR MEASURING AND REDUCING DUST IN GRANULAR MATERIAL	
EP	10157117.2	2199267	METHOD FOR PURIFYING SILICON CARBIDE STRUCTURES CONTROLLING AGGLOMERATED POINT DEFECT AND OXYGEN CLUSTER FORMATION INDUCED BY THE LATERAL SURFACE OF A SILICON SINGLE CRYSTAL DURING CZ GROWTH	2199267
EP	07869313.2	2097923	METHODS FOR PRODUCING SMOOTH WAFERS	
EP	13166827.9	2637208	SEMICONDUCTOR WAFER WITH HIGH THERMAL CONDUCTIVITY	
EP	07762756.0	1994562	SEMICONDUCTOR WAFER WITH HIGH THERMAL CONDUCTIVITY	
EP	07798957.2	2036121	WAFER PLATFORM	
EP	09810475.5	2329516	BULK SILICON WAFER PRODUCT USEFUL IN THE MANUFACTURE OF THREE DIMENSIONAL MULTIGATE MOSFETS	
EP	08869803.0	2225070	NANOTOPOGRAPHY CONTROL AND OPTIMIZATION USING FEEDBACK FROM WARP DATA	

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EP	09792504.4	2327091	WAFER HOLDER FOR SUPPORTING A SEMICONDUCTOR WAFER DURING A THERMAL TREATMENT PROCESS	
EP	13155744.9	2597672	LOW THERMAL MASS SEMICONDUCTOR WAFER PLATE	
EP	13155747.2	2597673	LOW THERMAL MASS SEMICONDUCTOR WAFER BOAT	
EP	10713392.8	2414793	SYSTEMS AND METHODS FOR WEIGHING A PULLED OBJECT	
EP	10801780.7	2519962	METHODS FOR PROCESSING SILICON ON INSULATOR WAFERS	
EP	10801778.1	2519965	METHOD FOR THE PREPARATION OF A MULTI-LAYERED CRYSTALLINE STRUCTURE	
EP	10813025.3	2517233	METHODS FOR ANALYSIS OF WATER AND SUBSTRATES RINSED IN WATER	
EP	10813030.3	2517234	METHODS FOR MONITORING THE AMOUNT OF CONTAMINATION IMPARTED INTO SEMICONDUCTOR WAFERS DURING WAFER PROCESSING	
EP	11703798.6	2539928	METHODS FOR REDUCING THE WIDTH OF THE UNBONDED REGION IN SOI STRUCTURES AND WAFERS AND SOI STRUCTURES PRODUCED BY SUCH METHODS	
EP	11749531.7	2599118	SEMICONDUCTOR AND SOLAR WAFERS	
EP	11749530.9	2599117	SEMICONDUCTOR AND SOLAR WAFERS AND METHOD FOR PROCESSING SAME	
EP	11758894.7	2552644	HYDROSTATIC PAD PRESSURE MODULATION IN A SIMULTANEOUS DOUBLE SIDE WAFER GRINDER	
EP	11757935.9	2589075	METHODS FOR IN-SITU PASSIVATION OF SILICON-ON-INSULATOR WAFERS	
EP	11769977.7	2619787	ADAPTER RING FOR SILICON ELECTRODE	

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EP	10179080.6	2261958	PROCESS FOR MAKING NON-OXYGEN PRECIPITATING CZOCHRALSKI SILICON WAFERS	2261958
EP	06111930.1	1688519	LOW DEFECT DENSITY SILICON SUBSTANTIALLY FREE OF OXIDATION INDUCED STACKING FAULTS HAVING A VACANCY-DOMINATED CORE	
EP	05747497.5	1766927	SYSTEMS AND METHODS FOR MANUFACTURING GRANULAR MATERIAL, AND FOR MEASURING AND REDUCING DUST IN GRANULAR MATERIAL	
FR	01905374.3	1257697	PROCESS FOR PRODUCING A SILICON MELT	1257697
FR	05107781.6	1669478	NITROGEN-DOPED SILICON SUBSTANTIALLY FREE OF OXIDATION INDUCED STACKING FAULTS	1669478
FR	10177865.2	2295619	LOW DEFECT DENSITY SILICON HAVING A VACANCY-DOMINATED CORE SUBSTANTIALLY FREE OF OXIDATION INDUCED STACKING FAULTS	
FR	02789582.0	1446517	INTERMITTENT FEEDING TECHNIQUE FOR INCREASING THE MELTING RATE OF POLYCRYSTALLINE SILICON	1446517
FR	02773835.0	1493179	PROCESS FOR CONTROLLING DENUDEZED ZONE DEPTH IN AN IDEAL OXYGEN PRECIPITATING SILICON WAFER	1493179
FR	10152849.5	2177648	PROCESS FOR PREPARING SINGLE CRYSTAL SILICON USING CRUCIBLE ROTATION TO CONTROL TEMPERATURE GRADIENT	2177648
FR	05772987.3	1781843	PARTIALLY DEVITRIFIED CRUCIBLE	1781843
FR	05739906.5	1743364	PROCESS FOR METALLIC CONTAMINATION REDUCTION IN SILICON WAFERS	1743364
FR	10179629.0	2259291	PROCESS FOR METALLIC CONTAMINATION REDUCTION IN SILICON WAFERS	2259291
FR	5852293.9	1831436	CONTROLLING MELT-SOLID INTERFACE SHAPE OF A GROWING SILICON CRYSTAL USING A VARIABLE MAGNETIC FIELD	1831436
FR	05788988.3	1756337	MELTER ASSEMBLY AND METHOD FOR CHARGING A CRYSTAL PULLER WITH MOLTEN SOURCE MATERIAL	1756337

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FR	5852345.7	1848844	ELETROMAGNETIC PUMPING OF LIQUID SILICON IN A CRYSTAL GROWING PROCESS	1848844
FR	05711676.6	1735127	WAFER CLAMPING DEVICE FOR A DOUBLE SIDE GRINDER	1735127
FR	10157117.2	2199267	METHOD FOR PURIFYING SILICON CARBIDE STRUCTURES	2199267
FR	07797092.9	1981685	DOUBLE SIDE WAFER GRINDER AND METHODS FOR ASSESSING WORKPIECE NANOTOPOLOGY	1981685
FR	08848771.5	2215290	REDUCTION OF AIR POCKETS IN SILICON CRYSTALS BY AVOIDING THE INTRODUCTION OF NEARLY-INSOLUBLE GASES INTO THE MELT	2215290
FR	09727521.8	2260507	METHODS FOR ETCHING THE EDGE OF A SILICON WAFER	2260507
FR	08771365.7	2165358	SUSCEPTOR FOR IMPROVING THROUGHPUT AND REDUCING WAFER DAMAGE	2165358
FR	08866204.4	2222901	EPITAXIAL BARREL SUSCEPTOR HAVING IMPROVED THICKNESS UNIFORMITY	2222901
FR	8869803	2225070	NANOTOPOGRAPHY CONTROL AND OPTIMIZATION USING FEEDBACK FROM WARP DATA	2225070
FR	09791617.5	2321617	METHOD AND DEVICE FOR CONTINUOUSLY MEASURING SILICON ISLAND ELEVATION	2321617
FR	09774069.0	2311080	LOW THERMAL MASS SEMICONDUCTOR WAFER SUPPORT	2311080
FR	09791232.3	2321450	GENERATING A PUMPING FORCE IN A SILICON MELT BY APPLYING A TIME-VARYING MAGNETIC FIELD	2321450
FR	10713392.8	2414793	SYSTEMS AND METHODS FOR WEIGHING A PULLED OBJECT	2414793
FR	04756166.7	1641964	PROCESS FOR PREPARING A STABILIZED IDEAL OXYGEN PRECIPITATING SILICON WAFER	1641964

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FR	03779446.8	1560951	PROCESS FOR PREPARING SINGLE CRYSTAL SILICON USING CRUCIBLE ROTATION TO CONTROL TEMPERATURE GRADIENT	1560951
FR	05024867.3	1624482	THERMALLY ANNEALED WAFERS HAVING IMPROVED INTERNAL GETTERING	1624482
FR	07023865.4	1914796	METHOD OF FORMING NON-OXYGEN PRECIPITATING CZOCHRALSKI SILICON WAFERS	1914796
FR	10179080.6	2261958	PROCESS FOR MAKING NON-OXYGEN PRECIPITATING CZOCHRALSKI SILICON WAFERS	2261958
FR	1930582.0	1287187	MODIFIED SUSCEPTOR FOR USE IN CHEMICAL VAPOR DEPOSITION PROCESS	1287187
FR	01930651.3	1287188	EPITAXIAL SILICON WAFER FREE FROM AUTODOPING AND BACKSIDE HALO	1287188
FR	02720794.3	1348048	PROCESS FOR PREPARING SINGLE CRYSTAL SILICON HAVING IMPROVED GATE OXIDE INTEGRITY	1348048
FR	01968299.6	1325178	NITROGEN-DOPED SILICON SUBSTANTIALLY FREE OF OXIDATION INDUCED STACKING FAULTS	1325178
FR	02714762.8	1356139	LOW DEFECT DENSITY SILICON SUBSTANTIALLY FREE OF OXIDATION INDUCED STACKING FAULTS HAVING A VACANCY-DOMINATED CORE	1356139
FR	3768900.7	1560950	A CRYSTAL PULLER AND METHOD FOR GROWING A MONOCRYSTALLINE INGOT	1560950
FR	05763307.5	1791799	METHOD FOR PURIFYING SILICON CARBIDE COATED STRUCTURES	1791799
FR	95917044.0	0758941	SEMICONDUCTOR WAFER POLISHING APPARATUS AND METHOD	0758941
FR	96304342.7	0748885	SURFACE-TREATED CRUCIBLES FOR IMPROVED ZERO DISLOCATION PERFORMANCE	0748885
FR	96304341.9	0753605	METHODS FOR IMPROVING ZERO DISLOCATION YIELD OF SINGLE CRYSTALS	0753605

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FR	96303047.3	0745830	SYSTEM AND METHOD FOR CONTROLLING GROWTH OF A SILICON CRYSTAL	0745830
FR	96304813.7	0756024	METHOD FOR PREPARING MOLTEN SILICON MELT FROM POLYCRYSTALLINE SILICON CHARGE	0756024
FR	96301616.7	0732431	PRECISION CONTROLLED PRECIPITATION OF OXYGEN IN SILICON	0732431
FR	96303755.1	0747511	APPARATUS FOR ROTATING A CRUCIBLE OF A CRYSTAL PULLING MACHINE	0747511
FR	98906703.8	1002335	IDEAL OXYGEN PRECIPITATING SILICON WAFERS AND OXYGEN OUT-DIFFUSION-LESS PROCESS THEREFOR	1002335
FR	2027280.3	1300879	IDEAL OXYGEN PRECIPITATING SILICON WAFERS AND OXYGEN OUT-DIFFUSION-LESS PROCESS THEREFOR	1300879
FR	98918113.6	0973963	LOW DEFECT DENSITY SINGLE CRYSTAL SILICON	0973963
FR	01126017.1	1209258	LOW DEFECT DENSITY SINGLE CRYSTAL SILICON	1209258
FR	01130907.7	1209259	LOW DEFECT DENSITY, SELF-INTERSTITIAL DOMINATED SILICON	1209259
FR	98919752	0973964	LOW DEFECT DENSITY SINGLE CRYSTAL SILICON	0973964
FR	99930636.8	1090168	ELECTRICAL RESISTANCE HEATER AND METHOD FOR CRYSTAL GROWING APPARATUS	1090168
FR	98952124.0	1025288	PROCESS FOR PREPARING A SILICON MELT FROM A POLYSILICON CHARGE	1025288
FR	99927625.8	1090167	PROCESS AND APPARATUS FOR PREPARATION OF SILICON CRYSTALS WITH REDUCED METAL CONTENT	1090167
FR	98915353.1	0973962	LOW DEFECT DENSITY, IDEAL OXYGEN PRECIPITATING SILICON	0973962

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FR	01109372.1	1146150	LOW DEFECT DENSITY, IDEAL OXYGEN PRECIPITATING SILICON	1146150
FR	99903333.5	0972095	CRUCIBLE AND METHOD OF PREPARATION THEREOF	0972095
FR	99942012.8	1110236	NON-UNIFORM MINORITY CARRIER LIFETIME DISTRIBUTIONS IN HIGH PERFORMANCE SILICON POWER DEVICES	1110236
FR	99956561.7	1133590	EPITAXIAL SILICON WAFERS SUBSTANTIALLY FREE OF GROWN-IN DEFECTS	1133590B
FR	02021897.0	1273684	LOW DEFECT DENSITY, VACANCY DOMINATED SILICON	1273684
FR	98919749.6	0972094	LOW DEFECT DENSITY SINGLE CRYSTAL SILICON	0972094
FR	01107427.5	1118697	LOW DEFECT DENSITY, VACANCY DOMINATED SILICON	1118697
FR	99956562.5	1125008	THERMALLY ANNEALED, LOW DEFECT DENSITY SINGLE CRYSTAL SILICON	1125008
FR	99942528.3	1129471	THERMALLY ANNEALED WAFERS HAVING IMPROVED INTERNAL GETTERING	1129471
FR	00957400.5	1218571	PROCESS FOR PREPARING SINGLE CRYSTAL SILICON HAVING UNIFORM THERMAL HISTORY	1218571
FR	99945173.5	1114441	NON-OXYGEN PRECIPITATING CZOCHRALSKI SILICON WAFERS	1114441
FR	99944006.8	1110240	PROCESS FOR PREPARING AN IDEAL OXYGEN PRECIPITATING SILICON WAFER	1110240
FR	99930652.5	1090166	PROCESS FOR GROWTH OF DEFECT FREE SILICON CRYSTALS OF ARBITRARILY LARGE DIAMETERS	1090166
FR	00910080.3	1159470	HEAT SHIELD ASSEMBLY FOR CRYSTAL PULLER	1159470

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FR	99930653.3	1127175	PROCESS FOR GROWTH OF DEFECT FREE SILICON CRYSTALS OF ARBITRARILY LARGE DIAMETERS AT ARBITRARY GROWTH RATES MAXIMUM THROUGHOUT	1127175
FR	01991961.3	1330562	METHOD FOR THE PRODUCTION OF LOW DEFECT DENSITY SILICON	1330562
FR	01273548.6	1337697	METHOD FOR PREPARING MOLTEN SILICON MELT FROM POLYCRYSTALLINE SILICON CHARGE	1337697
FR	00916304.9	1169496	STRONTIUM DOPING OF MOLTEN SILICON FOR USE IN CRYSTAL GROWING PROCESS	1169496
FR	00914963.5	1175519	BARIUM DOPING OF MOLTEN SILICON FOR USE IN CRYSTAL GROWING PROCESS	1175519
FR	915791.8	1171652	METHOD AND SYSTEM FOR CONTROLLING DIAMETER OF A SILICON CRYSTAL IN A LOCKED SEED LIFT GROWTH PROCESS	1171652
FR	00961957.8	1222325	METHOD FOR PRODUCING CZOCHRALSKI SILICON FREE OF AGGLOMERATED SELF-INTERSTITIAL DEFECTS	1222325
FR	00963572.3	1222324	PROCESS FOR SUPPRESSING THE NUCLEATION AND/OR GROWTH OF INTERSTITIAL TYPE DEFECTS BY CONTROLLING THE COOLING RATE THROUGH NUCLEATION	1222324
FR	01273046.1	1332246	PROCESS FOR PREPARING LOW DEFECT DENSITY SILICON USING HIGH GROWTH RATES	1332246
GB	5852293.9	1831436	CONTROLLING MELT-SOLID INTERFACE SHAPE OF A GROWING SILICON CRYSTAL USING A VARIABLE MAGNETIC FIELD	1831436
GB	5852345.7	1848844	ELECTROMAGNETIC PUMPING OF LIQUID SILICON IN A CRYSTAL GROWING PROCESS	1848844
GB	95917044.0	0758941	SEMICONDUCTOR WAFER POLISHING APPARATUS AND METHOD	0758941
GB	96304342.7	0748885	SURFACE-TREATED CRUCIBLES FOR IMPROVED ZERO DISLOCATION PERFORMANCE	0748885
GB	96304341.9	0753605	METHODS FOR IMPROVING ZERO DISLOCATION YIELD OF SINGLE CRYSTALS	0753605

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GB	96303047.3	0745830	METHOD FOR CONTROLLING GROWTH OF A SILICON CRYSTAL	0745830
IT	5852293.9	1831436	CONTROLLING MELT-SOLID INTERFACE SHAPE OF A GROWING SILICON CRYSTAL USING A VARIABLE MAGNETIC FIELD	1831436
IT	5852345.7	1848844	ELETROMAGNETIC PUMPING OF LIQUID SILICON IN A CRYSTAL GROWING PROCESS	1848844
IT	95917044.0	0758941	SEMICONDUCTOR WAFER POLISHING APPARATUS AND METHOD	0758941
IT	96304342.7	0748885	SURFACE-TREATED CRUCIBLES FOR IMPROVED ZERO DISLOCATION PERFORMANCE	0748885
IT	96304341.9	0753605	METHODS FOR IMPROVING ZERO DISLOCATION YIELD OF SINGLE CRYSTALS	0753605
IT	96303047.3	0745830	METHOD FOR CONTROLLING GROWTH OF A SILICON CRYSTAL	0745830
JP	2008-188725	2009-029703A	LOW DEFECT DENSITY SILICON HAVING A VACANCY-DOMINATED CORE SUBSTANTIALLY FREE OF OXIDATION INDUCED STACKING FAULTS	4644729
JP	2012-250402	2013-058784	PROCESS FOR METALLIC CONTAMINATION REDUCTION IN SILICON WAFERS	
JP	2007-549377	2008526666	CONTROLLING MELT-SOLID INTERFACE SHAPE OF A GROWING SILICON CRYSTAL USING A VARIABLE MAGNETIC FIELD	
JP	2012-086178	2012-162453	SYSTEMS AND METHODS FOR MANUFACTURING GRANULAR MATERIAL, AND FOR MEASURING AND REDUCING DUST IN GRANULAR MATERIAL	
JP	2009-511251	2009-537442A	CONTROLLING AGGLOMERATED POINT DEFECT AND OXYGEN CLUSTER FORMATION INDUCED BY THE LATERAL SURFACE OF A SILICON SINGLE CRYSTAL DURING CZ GROWTH	5138678
JP	2009-544170	2010-515261	METHODS FOR PRODUCING SMOOTH WAFERS	5231449
JP	2008-553448	2009-525621A	DOUBLE SIDE WAFER GRINDER AND METHODS FOR ASSESSING WORKPIECE NANOTOPOLOGY	

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JP	2008-553453	2009-525622A	SEMICONDUCTOR WAFER WITH HIGH THERMAL CONDUCTIVITY	5261194
JP	2009-518475	2009-543352A	WAFER PLATFORM	
JP	2011525105	2012-501545	BULK SILICON WAFER PRODUCT USEFUL IN THE MANUFACTURE OF THREE DIMENSIONAL MULTIGATE MOSFETS	
JP	2011-503100	2011-521442	METHODS FOR ETCHING THE EDGE OF A SILICON WAFER	
JP	2012-237034	2013-093582	SUSCEPTOR FOR IMPROVING THROUGHPUT AND REDUCING WAFER DAMAGE	
JP	2010-540824	2011-508455	EPITAXIAL BARREL SUSCEPTOR HAVING IMPROVED THICKNESS UNIFORMITY	5237390
JP	2011-527019	2012-503312	WAFER HOLDER FOR SUPPORTING A SEMICONDUCTOR WAFER DURING A THERMAL TREATMENT PROCESS	
JP	2011-525085	2012-500775	METHOD AND DEVICE FOR CONTINUOUSLY MEASURING SILICON ISLAND ELEVATION	
JP	2011-516769	2011-526876	CONTROLLING A MELT-SOLID INTERFACE SHAPE OF A GROWING SILICON CRYSTAL USING AN UNBALANCED MAGNETIC FIELD AND ISO-ROTATION	
JP	2011-516492	2011-527109	LOW THERMAL MASS SEMICONDUCTOR WAFER SUPPORT	5436552
JP	2011-522248	2011-530474	GENERATING A PUMPING FORCE IN A SILICON MELT BY APPLYING A TIME-VARYING MAGNETIC FIELD	
JP	2011-537533	2012-509599	METHOD AND SYSTEM FOR STRIPPING THE EDGE OF A SEMICONDUCTOR WAFER	
JP	2012-503485	2012-522250	SYSTEMS AND METHODS FOR WEIGHING A PULLED OBJECT	
JP	2012-547180	2013-516085	METHODS FOR PROCESSING SILICON ON INSULATOR WAFERS	

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JP	2012-547160	2013-516767	METHOD FOR THE PREPARATION OF A MULTI-LAYERED CRYSTALLINE STRUCTURE	
JP	2012-545504	2013-516062	METHODS FOR ANALYSIS OF WATER AND SUBSTRATES RINSED IN WATER	
JP	2012-545505	2013-516063	METHODS FOR MONITORING THE AMOUNT OF CONTAMINATION IMPARTED INTO SEMICONDUCTOR WAFERS DURING WAFER PROCESSING	
JP	2012-545503	2013-516061	SEMICONDUCTOR WAFER TRANSPORT SYSTEM	
JP	2012-555018	2013-520838	METHODS FOR REDUCING THE WIDTH OF THE UNBONDED REGION IN SOI STRUCTURES AND WAFERS AND SOI STRUCTURES PRODUCED BY SUCH METHODS	
JP	2013-500633	2013-524484	HYDROSTATIC PAD PRESSURE MODULATION IN A SIMULTANEOUS DOUBLE SIDE WAFER GRINDER	
JP	2013-508588	2013-532370	WAFER SUPPORT RING	
JP	2006-518685	2007-534579A	PROCESS FOR PREPARING A STABILIZED IDEAL OXYGEN PRECIPITATING SILICON WAFER	4733029
JP	2004-551660	2006-506305A	PROCESS FOR PREPARING SINGLE CRYSTAL SILICON USING CRUCIBLE ROTATION TO CONTROL TEMPERATURE GRADIENT	4764007
JP	2009-046375	2009-239269A	NON-UNIFORM MINORITY CARRIER LIFETIME DISTRIBUTIONS IN HIGH PERFORMANCE SILICON POWER DEVICES	5405856
JP	2009-173150	2010-004054A	THERMALLY ANNEALED WAFERS HAVING IMPROVED INTERNAL GETTERING	4681063
JP	2009-23974	2009-147357A	SILICON ON INSULATOR STRUCTURE FROM LOW DEFECT DENSITY SINGLE CRYSTAL SILICON	
JP	2008-314569	2009-094533A	NON-OXYGEN PRECIPITATING CZOCHRALSKI SILICON WAFERS	4448547
JP	2010-155726	2010-265172	PROCESS FOR PREPARING LOW DEFECT DENSITY SILICON USING HIGH GROWTH RATES	

Crty	App Number	Pub Number	Title	Patent Number
JP	2001-559914	2003-522716A	PROCESS FOR PRODUCING A SILICON MELT	4335489
JP	2002-566012	2004-525057A	PROCESS FOR PREPARING SINGLE CRYSTAL SILICON HAVING IMPROVED GATE OXIDE INTEGRITY	4554886
JP	2002-559879	2005-506261A	LOW DEFECT DENSITY SILICON HAVING A VACANCY-DOMINATED CORE SUBSTANTIALLY FREE OF OXIDATION INDUCED STACKING FAULTS	4439810
JP	2003-545864	2005515951	INTERMITTENT FEEDING TECHNIQUE FOR INCREASING THE MELTING RATE OF POLYCRYSTALLINE SILICON	4233453
JP	2004-552119	2006-506306A	A CRYSTAL PULLER AND METHOD FOR GROWING A MONOCRYSTALLINE INGOT	4486889
JP	2007-522572	2008-507467A	PARTIALLY DEVITRIFIED CRUCIBLE	5127451
JP	2007-511422	2007-536738A	PROCESS FOR METALLIC CONTAMINATION REDUCTION IN SILICON WAFERS	5238251
JP	2007-516496		SYSTEMS AND METHODS FOR MANUFACTURING GRANULAR MATERIAL, AND FOR MEASURING AND REDUCING DUST IN GRANULAR MATERIAL	5032308
JP	2007-516754	2008-503427A	MELTER ASSEMBLY AND METHOD FOR CHARGING A CRYSTAL PULLER WITH MOLTEN SOURCE MATERIAL	5080971
JP	2007-503897		WAFER CLAMPING DEVICE FOR A DOUBLE SIDE GRINDER	4948390
JP	2007-523543		METHOD FOR PURIFYING SILICON CARBIDE COATED STRUCTURES	5103178
JP	2006-151959		SEMICONDUCTOR WAFER POLISHING APPARATUS AND METHOD	4012927
JP	154336/1996		SURFACE-TREATED CRUCIBLES FOR IMPROVED ZERO DISLOCATION PERFORMANCE	3046545
JP	2000-513316		PROCESS FOR THE PREPARATION OF SILICON WAFERS HAVING A CONTROLLED DISTRIBUTION OF OXYGEN PRECIPITATE NUCLEATION CENTERS	4302879

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JP	154337/1996		METHODS FOR IMPROVING ZERO DISLOCATION YIELD OF SINGLE CRYSTALS	3054362
JP	144105/1996		SILICON SINGLE CRYSTAL HAVING ELIMINATED DISLOCATION IN ITS NECK	3969766
JP	194487/1996	3856873	METHOD FOR PREPARING MOLTEN SILICON MELT FROM POLYCRYSTALLINE SILICON CHARGE	3856873
JP	144110/1996		APPARATUS FOR ROTATING A CRUCIBLE OF A CRYSTAL PULLING MACHINE	3969767
JP	537814/1998		IDEAL OXYGEN PRECIPITATING SILICON WAFERS AND OXYGEN OUT-DIFFUSION-LESS PROCESS THEREFOR	3288721
JP	2002-303260		LOW DEFECT DENSITY, IDEAL OXYGEN PRECIPITATING SILICON	4324362
JP	2002-303285		LOW DEFECT DENSITY SILICON	4291559
JP	2005-326511	2006-131500A	LOW DEFECT DENSITY, IDEAL OXYGEN PRECIPITATING SILICON	4322859
JP	2005-309456	2006-086779A	LOW DEFECT DENSITY SINGLE CRYSTAL SILICON	4313356
JP	543182/1998		LOW DEFECT DENSITY SINGLE CRYSTAL SILICON	3449730
JP	543189/1998		LOW DEFECT DENSITY SINGLE CRYSTAL SILICON	3449731
JP	2002-303272	3782387	LOW DEFECT DENSITY SINGLE CRYSTAL SILICON	3782387
JP	2000-557023	2003-522086A	ELECTRICAL RESISTANCE HEATER FOR CRYSTAL GROWING APPARATUS AND ITS METHOD OF USE	4567192
JP	2000-517130		PROCESS FOR PREPARING A SILICON MELT FROM A POLYSILICON CHARGE	4225688

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JP	2000-554909	2002-518286A	PROCESS AND APPARATUS FOR PREPARATION OF SILICON CRYSTALS WITH REDUCED METAL CONTENT	4683725
JP	543063/1998		LOW DEFECT DENSITY SINGLE CRYSTAL SILICON	3449729
JP	540471/1999		CRUCIBLE AND METHOD OF PREPARATION THEREOF	4347916
JP	2000-564229		NON-UNIFORM MINORITY CARRIER LIFETIME DISTRIBUTIONS IN HIGH PERFORMANCE SILICON POWER DEVICES	4312385
JP	2000-576082		EPITAXIAL SILICON WAFERS SUBSTANTIALLY FREE OF GROWN-IN DEFECTS	3904832
JP	2002-303232	2003-192492A	LOW DEFECT DENSITY SINGLE CRYSTAL SILICON	4298523
JP	2004-054483	2004-155655A	LOW DEFECT DENSITY SINGLE CRYSTAL SILICON	4274973
JP	2005-318604	2006-062960A	LOW DEFECT DENSITY SINGLE CRYSTAL SILICON	4477569
JP	543181/1998		LOW DEFECT DENSITY SINGLE CRYSTAL SILICON	3544676
JP	2000-576083		THERMALLY ANNEALED, LOW DEFECT DENSITY SINGLE CRYSTAL SILICON	4875800
JP	2000-568103		THERMALLY ANNEALED WAFERS HAVING IMPROVED INTERNAL GETTERING	4405082
JP	2001-519945		PROCESS FOR PREPARING SINGLE CRYSTAL SILICON HAVING UNIFORM THERMAL HISTORY	4700874
JP	2000-568118		IDEAL OXYGEN PRECIPITATING SILICON WAFERS AND OXYGEN OUT-DIFFUSION-LESS PROCESS THEREFOR	4405083
JP	2005-261049	2006-036635A	PROCESS FOR GROWTH OF DEFECT FREE SILICON CRYSTALS OF ARBITRARILY LARGE DIAMETERS AT ARBITRARY GROWTH RATES MAXIMUM THROUGHOUT	4284310

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JP	2000-576081		PROCESS FOR GROWTH OF DEFECT FREE SILICON CRYSTALS OF ARBITRARILY LARGE DIAMETERS AT ARBITRARY GROWTH RATES MAXIMUM THROUGHOUT	3737364
JP	2002-579645	2004-531446A	METHOD FOR PREPARING MOLTEN SILICON MELT FROM POLYCRYSTALLINE SILICON CHARGE	4287657
JP	2000-605809	2002-539069A	STRONTIUM DOPING OF MOLTEN SILICON FOR USE IN CRYSTAL GROWING PROCESS	4439741
JP	2000-605808	2002-539068A	BARIUM DOPING OF MOLTEN SILICON FOR USE IN CRYSTAL GROWING PROCESS	4560216
JP	2000-606813	2003-528017A	METHOD AND SYSTEM FOR CONTROLLING DIAMETER OF A SILICON CRYSTAL IN A LOCKED SEED LIFT GROWTH PROCESS	4602561
JP	2001-525019		METHOD FOR PRODUCING CZOCHRALSKI SILICON FREE OF AGGLOMERATED SELF-INTERSTITIAL DEFECTS	4360770
JP	2002-574410		PROCESS FOR PREPARING LOW DEFECT DENSITY SILICON USING HIGH GROWTH RATES	4611612
JP	2001-582617		MODIFIED SUSCEPTOR FOR USE IN CHEMICAL VAPOR DEPOSITION PROCESS	4492840
JP	2001-582618		AN EPITAXIAL SILICON WAFER FREE FROM AUTODOPING AND BACKSIDE HALO AND A METHOD AND APPARATUS FOR THE PREPARATION THEREOF	4263410
JP	138195/1996		METHOD FOR CONTROLLING GROWTH OF A SILICON CRYSTAL	4018172
KR	10-2007-7008791		NITROGEN-DOPED SILICON SUBSTANTIALLY FREE OF OXIDATION INDUCED STACKING FAULTS	816207
KR	10-2007-7006547		LOW DEFECT DENSITY SILICON HAVING A VACANCY-DOMINATED CORE SUBSTANTIALLY FREE OF OXIDATION INDUCED STACKING FAULTS	805518
KR	10-2007-7006698		IDEAL OXYGEN PRECIPITATING SILICON WAFERS WITH NITROGEN/CARBON STABILIZED OXYGEN PRECIPITATE NUCLEATION CENTERS AND PROCESS FOR MAKING THE SAME	10-0920862
KR	10-2009-7015328		IDEAL OXYGEN PRECIPITATING SILICON WAFERS WITH NITROGEN/CARBON STABILIZED OXYGEN PRECIPITATE NUCLEATION CENTERS AND PROCESS FOR MAKING THE SAME	10-0973393

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KR	10-2007-7006666	20070038578	INTERMITTENT FEEDING TECHNIQUE FOR INCREASING THE MELTING RATE OF POLYCRYSTALLINE SILICON	860440
KR	10-2007-7015069		CONTROLLING MELT-SOLID INTERFACE SHAPE OF A GROWING SILICON CRYSTAL USING A VARIABLE MAGNETIC FIELD	10-1009074
KR	10-2007-7015050		ELECTROMAGNETIC PUMPING OF LIQUID SILICON IN A CRYSTAL GROWING PROCESS	10-0986903
KR	10-2009-7003961	20090028656	WAFER CLAMPING DEVICE FOR A DOUBLE SIDE GRINDER	10-1141474
KR	10-2008-7031022	20090024172	CONTROLLING AGGLOMERATED POINT DEFECT AND OXYGEN CLUSTER FORMATION INDUCED BY THE LATERAL SURFACE OF A SILICON SINGLE CRYSTAL DURING CZ GROWTH	
KR	10-2008-7021294	20080090558	DOUBLE SIDE WAFER GRINDER AND METHODS FOR ASSESSING WORKPIECE NANOTOPOLOGY	10-1247065
KR	10-2008-7021333	2008098632	SEMICONDUCTOR WAFER WITH HIGH THERMAL CONDUCTIVITY	
KR	10-2010-7012963	20100100872	REDUCTION OF AIR POCKETS IN SILICON CRYSTALS BY AVOIDING THE INTRODUCTION OF NEARLY-INSOLUBLE GASES INTO THE MELT	
KR	10-2010-7016660	20100102185	SUSCEPTOR WITH SUPPORT BOSSES	
KR	10-2004-7016046	10-2004-99416	PROCESS FOR CONTROLLING DENUDED ZONE DEPTH IN AN IDEAL OXYGEN PRECIPITATING SILICON WAFER	10-0745309
KR	10-2006-7000480		PROCESS FOR PREPARING A STABILIZED IDEAL OXYGEN PRECIPITATING SILICON WAFER	810367
KR	10-2005-7008532		PROCESS FOR PREPARING SINGLE CRYSTAL SILICON USING CRUCIBLE ROTATION TO CONTROL TEMPERATURE GRADIENT	10-0764394
KR	2000-7002428		LOW DEFECT DENSITY, SELF-INTERSTITIAL DOMINATED SILICON	491823
KR	10-2002-7010470	2002-81324	PROCESS FOR PRODUCING A SILICON MELT	10-705526

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KR	10-2003-7008949	2003-76598	PROCESS FOR PREPARING SINGLE CRYSTAL SILICON HAVING IMPROVED GATE OXIDE INTEGRITY	10-0708788
KR	10-2006-7025485		PROCESS FOR PREPARING SINGLE CRYSTAL SILICON HAVING IMPROVED GATE OXIDE INTEGRITY	708789
KR	10-2003-7013383		CONTROL OF THERMAL DONOR FORMATION IN HIGH RESISTIVITY CZ SILICON	10-0745312
KR	10-2006-7026471		NITROGEN-DOPED SILICON SUBSTANTIALLY FREE OF OXIDATION INDUCED STACKING FAULTS	10-0917087
KR	10-2003-7009878		LOW DEFECT DENSITY SILICON SUBSTANTIALLY FREE OF OXIDATION INDUCED STACKING FAULTS HAVING A VACANCY-DOMINATED CORE	854186
KR	10-2004-7009784	10-2004-76872	IDEAL OXYGEN PRECIPITATING SILICON WAFERS WITH NITROGEN/CARBON STABILIZED OXYGEN PRECIPITATE NUCLEATION CENTERS AND PROCESS FOR MAKING THE SAME	10-0745308
KR	10-2004-7007450	20050044493	INTERMITTENT FEEDING TECHNIQUE FOR INCREASING THE MELTING RATE OF POLYCRYSTALLINE SILICON	811989
KR	10-2005-7008505	20050086573	A CRYSTAL PULLER AND METHOD FOR GROWING A MONOCRYSTALLINE INGOT	10-1181052
KR	10-2007-7004180	2007059064	PARTIALLY DEVITRIFIED CRUCIBLE	10-1251674
KR	10-2006-7025661		PROCESS FOR METALLIC CONTAMINATION REDUCTION IN SILICON WAFERS	10-1165108
KR	10-2007-7001156	20070042971	A MELTER ASSEMBLY AND METHOD FOR CHARGING A CRYSTAL FORMING APPARATUS WITH MOLTEN SOURCE MATERIAL	
KR	10-2007-7004664	20070073736	METHOD FOR PURIFYING SILICON CARBIDE COATED STRUCTURES	10-1201164
KR	706425/1996		SEMICONDUCTOR WAFER POLISHING APPARATUS AND METHOD	371762
KR	1996-21255		SURFACE-TREATED CRUCIBLES FOR IMPROVED ZERO DISLOCATION PERFORMANCE	408905

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KR	1996-21256		METHODS FOR IMPROVING ZERO DISLOCATION YIELD OF SINGLE CRYSTALS	408906
KR	17506/1996		METHOD FOR CONTROLLING GROWTH OF A SILICON CRYSTAL	426419
KR	28850/1996		METHOD FOR PREPARING MOLTEN SILICON MELT FROM POLYCRYSTALLINE SILICON CHARGE	411963
KR	52513/1997		PROCESS FOR CONTROLLING THE OXYGEN CONTENT IN SILICON WAFERS HEAVILY DOPED WITH ANTIMONY OR ARSENIC	563425
KR	7007814/1999		IDEAL OXYGEN PRECIPITATING SILICON WAFERS AND OXYGEN OUT-DIFFUSION-LESS PROCESS THEREFOR	10-395391
KR	7009309/1999		LOW DEFECT DENSITY SINGLE CRYSTAL SILICON	508048
KR	2000-7001047		HEAT SHIELD ASSEMBLY AND METHOD OF GROWING VACANCY RICH SINGLE CRYSTAL SILICON	491384
KR	2000-7004080		PROCESS FOR PREPARING A SILICON MELT FROM A POLYSILICON CHARGE	506288
KR	2000-7014047		PROCESS AND APPARATUS FOR PREPARATION OF SILICON CRYSTALS WITH REDUCED METAL CONTENT	622331
KR	1999-7009006		CRUCIBLE AND METHOD OF PREPARATION THEREOF	10-0714136
KR	10-2001-7001508		NON-UNIFORM MINORITY CARRIER LIFETIME DISTRIBUTIONS IN HIGH PERFORMANCE SILICON POWER DEVICES	498943
KR	2001-7004280		THERMALLY ANNEALED, LOW DEFECT DENSITY SINGLE CRYSTAL SILICON	622884
KR	2001-7002617		THERMALLY ANNEALED SILICON WAFERS HAVING IMPROVED INTERNAL GETTERING	816696
KR	10-20027002865	1020020026379	PROCESS FOR PREPARING SINGLE CRYSTAL SILICON HAVING UNIFORM THERMAL HISTORY	0717237

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KR	10-2001-7002717		SILICON ON INSULATOR STRUCTURE FROM LOW DEFECT DENSITY SINGLE CRYSTAL SILICON	581305
KR	2001-7002599		NON-OXYGEN PRECIPITATING CZOCHRALSKI SILICON WAFERS	10-0770190
KR	2001-7002616		IDEAL OXYGEN PRECIPITATING SILICON WAFERS AND OXYGEN OUT-DIFFUSION-LESS PROCESS THEREFOR	10-0957729
KR	2001-7010856		HEAT SHIELD ASSEMBLY FOR CRYSTAL PULLER	10-687511
KR	10-2000-7011785	1020010042959	PROCESS FOR GROWTH OF DEFECT FREE SILICON CRYSTALS OF ARBITRARILY LARGE DIAMETERS AT ARBITRARY GROWTH RATES MAXIMUM THROUGHOUT	526081
KR	10-2003-7006117		METHOD FOR THE PRODUCTION OF LOW DEFECT DENSITY SILICON	10-0687664
KR	10-2003-7006272		METHOD FOR PREPARING MOLTEN SILICON MELT FROM POLYCRYSTALLINE SILICON CHARGE	10-0689300
KR	2001-7010997		STRONTIUM DOPING OF MOLTEN SILICON FOR USE IN CRYSTAL GROWING PROCESS	0681744
KR	2001-7011680		BARIUM DOPING OF MOLTEN SILICON FOR USE IN CRYSTAL GROWING PROCESS	719821
KR	2001-7011729		METHOD AND SYSTEM FOR CONTROLLING DIAMETER OF A SILICON CRYSTAL IN A LOCKED SEED LIFT GROWTH PROCESS	10-0690218
KR	102002-7003800		METHOD FOR PRODUCING CZOCHRALSKI SILICON FREE OF AGGLOMERATED SELF-INTERSTITIAL DEFECTS	10-0778194
KR	102002-7003802		PROCESS FOR SUPPRESSING THE NUCLEATION AND/OR GROWTH OF INTERSTITIAL TYPE DEFECTS BY CONTROLLING THE COOLING RATE THROUGH NUCLEATION	745311
KR	10-2003-7006115		PROCESS FOR PREPARING LOW DEFECT DENSITY SILICON USING HIGH GROWTH RATES	10-0669299
KR	10-2002-7015043		MODIFIED SUSCEPTOR FOR USE IN CHEMICAL VAPOR DEPOSITION PROCESS	784001

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KR	10-2002-7015042		EPITAXIAL SILICON WAFER FREE FROM AUTODOPING AND BACKSIDE HALO	726301
MY	PI 95001261		SEMICONDUCTOR WAFER POLISHING APPARATUS AND METHOD	MY-116349-A
MY	9602380		SURFACE-TREATED CRUCIBLES FOR IMPROVED ZERO DISLOCATION PERFORMANCE	• MY-112218A
MY	PI 96002395		METHODS FOR IMPROVING ZERO DISLOCATION YIELD OF SINGLE CRYSTALS	MY-113247A
MY	PI96001602		METHOD FOR CONTROLLING GROWTH OF A SILICON CRYSTAL	MY-120292-A
MY	PI 98000816		IDEAL OXYGEN PRECIPITATING SILICON WAFERS AND OXYGEN OUT-DIFFUSION-LESS PROCESS THEREFOR	MY-132868-A
MY	PI 98001569		LOW DEFECT DENSITY SINGLE CRYSTAL SILICON	MY-120441-A
MY	PI 20041399		LOW DEFECT DENSITY SINGLE CRYSTAL SILICON	MY127383-A
MY	PI 98001563		LOW DEFECT DENSITY SELF-INTERSTITIAL DOMINATED SILICON	MY-120036-A
MY	PI20042147		LOW DEFECT DENSITY SELF-INTERSTITIAL DOMINATED SILICON	MY-127584-A
MY	PI 98001560		PROCESS FOR PRODUCING LOW DEFECT DENSITY, IDEAL OXYGEN PRECIPITATING SILICON	MY-137778-A
MY	PI 20042494		PROCESS FOR PRODUCING LOW DEFECT DENSITY, IDEAL OXYGEN PRECIPITATING SILICON	MY135749-A
MY	PI 98001561		LOW DEFECT DENSITY SINGLE CRYSTAL SILICON	MY-132874-A
MY	PI20041774	MY-127594-A	LOW DEFECT DENSITY SINGLE CRYSTAL SILICON	MY-127594-A

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SG	200704499-3	133252	CONTROLLING MELT-SOLID INTERFACE SHAPE OF A GROWING SILICON CRYSTAL USING A VARIABLE MAGNETIC FIELD	133252
SG	201006529-0	0165352	CONTROLLING AGGLOMERATED POINT DEFECT AND OXYGEN CLUSTER FORMATION INDUCED BY THE LATERAL SURFACE OF A SILICON SINGLE CRYSTAL DURING CZ GROWTH	165352
SG	200808326-3		CONTROLLING AGGLOMERATED POINT DEFECT AND OXYGEN CLUSTER FORMATION INDUCED BY THE LATERAL SURFACE OF A SILICON SINGLE CRYSTAL DURING CZ GROWTH	147702
SG	200805494-2		DOUBLE SIDE WAFER GRINDER AND METHODS FOR ASSESSING WORKPIECE NANOTOPOLOGY	144608
SG	200805571-7		SEMICONDUCTOR WAFER WITH HIGHLY DOPED PROTECTIVE LAYER	P144650
SG	200809106-8		WAFER PLATFORM	148504
SG	201005798-2		CARBON NANOTUBE REINFORCED WIRESAW BEAM USING IN WIRESAW SLICING OF INGOTS INTO WAFERS	163913
SG	201003030-2		REDUCTION OF AIR POCKETS IN SILICON CRYSTALS BY AVOIDING THE INTRODUCTION OF NEARLY-INSOLUBLE GASES INTO THE MELT	161032
SG	201003884-2		EPITAXIAL BARREL SUSCEPTOR HAVING IMPROVED THICKNESS UNIFORMITY	162105
SG	201003883-4		SUSCEPTOR WITH SUPPORT BOSSES	162104
SG	201209204-5	0186653	SUSCEPTOR WITH SUPPORT BOSSES	
SG	201003886-7	162106	NANOTOPOGRAPHY CONTROL AND OPTIMIZATION USING FEEDBACK FROM WARP DATA	162106
SG	201103600-1		METHOD AND SYSTEM FOR STRIPPING THE EDGE OF A SEMICONDUCTOR WAFER	171343
SG	201107072-9	0174608	SYSTEMS AND METHODS FOR WEIGHING A PULLED OBJECT	

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SG	201204185-1	0181556	METHODS FOR PROCESSING SILICON ON INSULATOR WAFERS	
SG	201204838-5	0181986	METHOD FOR THE PREPARATION OF A MULTI-LAYERED CRYSTALLINE STRUCTURE	
SG	201203605-9	0181426	METHODS FOR ANALYSIS OF WATER AND SUBSTRATES RINSED IN WATER	
SG	201203606-7	0181427	METHODS FOR MONITORING THE AMOUNT OF CONTAMINATION IMPARTED INTO SEMICONDUCTOR WAFERS DURING WAFER PROCESSING	
SG	201303262-8	0189816	METHODS FOR REDUCING THE WIDTH OF THE UNBONDED REGION IN SOI STRUCTURES AND WAFERS AND SOI STRUCTURES PRODUCED BY SUCH METHODS	
SG	201205785-7	0183175	METHODS FOR REDUCING THE WIDTH OF THE UNBONDED REGION IN SOI STRUCTURES AND WAFERS AND SOI STRUCTURES PRODUCED BY SUCH METHODS	183175
SG	201300261-3	0187054	SEMICONDUCTOR AND SOLAR WAFERS	187054
SG	201300265-4	0187058	SEMICONDUCTOR AND SOLAR WAFERS AND METHOD FOR PROCESSING SAME	
SG	201206736-9	0184014	HYDROSTATIC PAD PRESSURE MODULATION IN A SIMULTANEOUS DOUBLE SIDE WAFER GRINDER	
SG	201209602-0	0186853	METHODS FOR IN-SITU PASSIVATION OF SILICON-ON-INSULATOR WAFERS	
SG	200700505.1		PARTIALLY DEVITRIFIED CRUCIBLE	129174
SG	200608808-2		MELTER ASSEMBLY AND METHOD FOR CHARGING A CRYSTAL PULLER WITH MOLTEN SOURCE MATERIAL	128268
SG	200606446-3		WAFER CLAMPING DEVICE FOR A DOUBLE SIDE GRINDER	125576
SG	9610054-0	0050738	SURFACE-TREATED CRUCIBLES FOR IMPROVED ZERO DISLOCATION PERFORMANCE	50738

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SG	9610055-7	0055205	METHODS FOR IMPROVING ZERO DISLOCATION YIELD OF SINGLE CRYSTALS	P-55205
SG	9609939-5	0047146	SYSTEM AND METHOD FOR CONTROLLING GROWTH OF A SILICON CRYSTAL	47146
SG	9904042-0		IDEAL OXYGEN PRECIPITATING SILICON WAFERS AND OXYGEN OUT-DIFFUSION-LESS PROCESS THEREFOR	67598
SG	9904917-3		LOW DEFECT DENSITY SINGLE CRYSTAL SILICON	68337
SG	200105492-3	0105510	LOW DEFECT DENSITY SILICON	105510
SG	9904900-9		LOW DEFECT DENSITY SINGLE CRYSTAL SILICON	68325
SG	200105490-7		LOW DEFECT DENSITY SINGLE CRYSTAL SILICON	105509
SG	200007398-1		ELECTRICAL RESISTANCE HEATER AND METHOD FOR CRYSTAL GROWING APPARATUS	78131
SG	200601434-4		LOW DEFECT DENSITY, IDEAL OXYGEN PRECIPITATING SILICON	151096
SG	9904737-5		LOW DEFECT DENSITY SINGLE CRYSTAL SILICON	68243
SG	200105905-4		LOW DEFECT DENSITY, IDEAL OXYGEN PRECIPITATING SILICON	105513
SG	9904738-3		LOW DEFECT DENSITY SINGLE CRYSTAL SILICON	68244
TW	096118095	200813268	CONTROLLING AGGLOMERATED POINT DEFECT AND OXYGEN CLUSTER FORMATION INDUCED BY THE LATERAL SURFACE OF A SILICON SINGLE CRYSTAL DURING CZ GROWTH	
TW	096149804	200847251	METHODS FOR PRODUCING SMOOTH WAFERS	

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TW	097143906	200932962	REDUCTION OF AIR POCKETS IN SILICON CRYSTALS BY AVOIDING THE INTRODUCTION OF NEARLY-INSOLUBLE GASES INTO THE MELT	
TW	098110667	201003758	METHOD FOR ETCHING THE EDGE OF A SILICON WAFER	
TW	100145643	201234487	PROCESS FOR ANNEALING SEMICONDUCTOR WAFERS WITH FLAT DOPANT DEPTH PROFILES	
TW	097122907	200910513	SUSCEPTOR FOR IMPROVING THROUGHPUT AND REDUCING WAFER DAMAGE	1352400
TW	097151004	200939384	EPITAXIAL BARREL SUSCEPTOR HAVING IMPROVED THICKNESS UNIFORMITY	1416650
TW	097151005	200943471	SUSCEPTOR WITH SUPPORT BOSSES	
TW	097151687	200946284	NANOTOPOGRAPHY CONTROL AND OPTIMIZATION USING FEEDBACK FROM WARP DATA	
TW	098122118	201005134	CONTROLLING A MELT-SOLID INTERFACE SHAPE OF A GROWING SILICON CRYSTAL USING AN UNBALANCED MAGNETIC FIELD AND ISO-ROTATION	
TW	098121898	201009998	LOW THERMAL MASS SEMICONDUCTOR WAFER SUPPORT	
TW	098126820	201012984	GENERATING A PUMPING FORCE IN A SILICON MELT BY APPLYING A TIME-VARYING MAGNETIC FIELD	
TW	098139383	201029094	METHOD AND SYSTEM FOR STRIPPING THE EDGE OF A SEMICONDUCTOR WAFER	
TW	099109224	201043931	SYSTEMS AND METHODS FOR WEIGHING A PULLED OBJECT	
TW	099146707	201140679	METHODS FOR PROCESSING SILICON ON INSULATOR WAFERS	
TW	099146704	201140662	METHOD FOR THE PREPARATION OF A MULTI-LAYERED CRYSTALLINE STRUCTURE	

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TW	099145319	201137999	SYSTEMS AND METHODS FOR ANALYSIS OF WATER AND SUBSTRATES RINSED IN WATER	
TW	100149841	201237222	MEASURING A CRYSTAL GROWTH FEATURE USING MULTIPLE CAMERAS	
TW	099145326	201138015	SEMICONDUCTOR WAFER TRANSPORT SYSTEM	
TW	100105495	201140694	METHODS FOR REDUCING THE WIDTH OF THE UNBONDED REGION IN SOI STRUCTURES AND WAFERS AND SOI STRUCTURES PRODUCED BY SUCH METHODS	
TW	100126836	201216341	SEMICONDUCTOR AND SOLAR WAFERS AND METHOD FOR PROCESSING SAME	
TW	100126842	201214701	SEMICONDUCTOR AND SOLAR WAFERS	
TW	100110457	201201264	HYDROSTATIC PAD PRESSURE MODULATION IN A SIMULTANEOUS DOUBLE SIDE WAFER GRINDER	
TW	100123193	201216414	METHODS FOR IN-SITU PASSIVATION OF SILICON-ON-INSULATOR WAFERS	
TW	100115489	201201318	WAFER SUPPORT RING	
TW	101103124	201250838	METHODS FOR REDUCING THE METAL CONTENT IN THE DEVICE LAYER OF SOI STRUCTURES AND SOI STRUCTURES PRODUCED BY SUCH METHODS	
TW	100134433	201218271	ADAPTER RING FOR SILICON ELECTRODE	
TW	101108941	201241994	SILICON ON INSULATOR STRUCTURES HAVING HIGH RESISTIVITY REGIONS IN THE HANDLE WAFER AND METHODS FOR PRODUCING SUCH STRUCTURES	
TW	101140405	201324676	CLAMPING APPARATUS FOR CLEAVING A BONDED WAFER STRUCTURE AND METHODS FOR CLEAVING	
TW	101142956	201326480	CRUCIBLES WITH A REDUCED AMOUNT OF BUBBLES, INGOTS AND WAFERS PRODUCED BY USE OF SUCH CRUCIBLES AND RELATED METHODS	

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TW	091124686	564500	PROCESS FOR CONTROLLING DENUDED ZONE DEPTH IN AN IDEAL OXYGEN PRECIPITATING SILICON WAFER	NI-191067
TW	093120519	200513551	PROCESS FOR PREPARING A STABILIZED IDEAL OXYGEN PRECIPITATING SILICON WAFER	1276539
TW	092131558	200426255	PROCESS FOR PREPARING SINGLE CRYSTAL SILICON USING CRUCIBLE ROTATION TO CONTROL TEMPERATURE GRADIENT	1251037
TW	90103244	1228552	PROCESS FOR PRODUCING A SILICON MELT	1228552
TW	091124527	1263707	PROCESS FOR PRODUCING A SILICON MELT	1263707
TW	90124688	1229154	HEAT SHIELD ASSEMBLY FOR CRYSTAL PULLING APPARATUS	1229154
TW	091107312	1256076	CONTROL OF THERMAL DONOR FORMATION IN HIGH RESISTIVITY CZ SILICON	1256076
TW	90123010	593799	NITROGEN-DOPED SILICON SUBSTANTIALLY FREE OF OXIDATION INDUCED STACKING FAULTS	NI-204081
TW	91101251	1222666	LOW DEFECT DENSITY SILICON SUBSTANTIALLY FREE OF OXIDATION INDUCED STACKING FAULTS	1222666
TW	091137013	200305932	EPITAXIAL SILICON WAFERS WITH NITROGEN/CARBON STABILIZED OXYGEN PRECIPITATION NUCLEI AND PROCESS FOR MAKING THE SAME	0276161
TW	091133508	250230	INTERMITTENT FEEDING TECHNIQUE FOR INCREASING THE MELTING RATE OF POLYCRYSTALLINE SILICON	1250230
TW	90120117	546724	METHOD AND APPARATUS FOR PROCESSING A SEMICONDUCTOR WAFER USING NOVEL FINAL POLISHING METHOD	NI-183576
TW	091113638	550681	PROCESS FOR PRODUCING SILICON ON INSULATOR STRUCTURE HAVING INTRINSIC GETTERING BY ION IMPLANTATION	NI-185044
TW	092131673	200417638	A CRYSTAL PULLER AND METHOD FOR GROWING A MONOCRYSTALLINE INGOT	1325900

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TW	094124802	200617219	PARTIALLY DEVITRIFIED CRUCIBLE	1338727
TW	094114777	200603224	PROCESS FOR METALLIC CONTAMINATION REDUCTION IN SILICON WAFERS	1393168
TW	094145407		CONTROLLING MELT-SOLID INTERFACE SHAPE OF A GROWING SILICON CRYSTAL USING A VARIABLE MAGNETIC FIELD	1369423
TW	094120351	200615405	SYSTEMS AND METHODS FOR MANUFACTURING GRANULAR MATERIAL, AND FOR MEASURING AND REDUCING DUST IN GRANULAR MATERIAL.	1361231
TW	095141552	200736422	ARSENIC AND PHOSPHORUS DOPED SILICON WAFER SUBSTRATES HAVING INTRINSIC GETTERING	1397619
TW	094120512	200617220	MELTER ASSEMBLY AND METHOD FOR CHARGING A CRYSTAL PULLER WITH MOLTEN SOURCE MATERIAL	1347377
TW	94145410	1360590	ELECTROMAGNETIC PUMPING OF LIQUID SILICON IN A CRYSTAL GROWING PROCESS	1360590
TW	094103075	200538235	WAFER CLAMPING DEVICE FOR A DOUBLE SIDE GRINDER	1289094
TW	094110383	200604131	METHOD FOR PURIFYING SILICON CARBIDE COATED STRUCTURES	10356813
TW	095102628	200636903	SEMICONDUCTOR WAFER BOAT FOR A VERTICAL FURNACE	
TW	096103059	200734149	WIRE SAW INGOT SLICING SYSTEM AND METHOD WITH INGOT PREHEATING, WEB PREHEATING, SLURRY TEMPERATURE CONTROL AND/OR SLURRY FLOW RATE CONTROL	1373405
TW	096103367	200800493	DOUBLE SIDE WAFER GRINDER AND METHODS FOR ASSESSING WORKPIECE NANOTOPOLOGY	1381906
TW	096103543	200801261	SEMICONDUCTOR WAFER WITH HIGH THERMAL CONDUCTIVITY	
TW	84101426		METHOD OF REGULATING CONCENTRATION AND DISTRIBUTION OF OXYGEN IN CZOCHRALSKI GROWN SILICON	NI-078839

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TW	85101500		SURFACE-TREATED CRUCIBLES FOR IMPROVED ZERO DISLOCATION PERFORMANCE	NI-106294
TW	87115764	448507	PROCESS FOR THE PREPARATION OF SILICON WAFERS HAVING A CONTROLLED DISTRIBUTION OF OXYGEN PRECIPITATE NUCLEATION CENTERS	NI-137452
TW	85101501		METHODS FOR IMPROVING ZERO DISLOCATION YIELD OF SINGLE CRYSTALS	NI-085440
TW	84112443		METHOD FOR CONTROLLING GROWTH OF A SILICON CRYSTAL	NI-81606
TW	84112470		METHOD FOR PREPARING MOL TEN SILICON MELT FROM POLYCRYSTALLINE SILICON CHARGE	NI-078572
TW	84111819		PRECISION CONTROLLED PRECIPITATION OF OXYGEN IN SILICON	NI-098002
TW	86114674	509731	PROCESS FOR CONTROLLING THE OXYGEN CONTENT IN SILICON WAFERS HEAVILY DOPED WITH ANTIMONY OR ARSENIC	NI-166399
TW	84113413	NI-084735	APPARATUS FOR ROTATING A CRUCIBLE OF A CRYSTAL PULLING MACHINE	300311
TW	87102740	528815	IDEAL OXYGEN PRECIPITATING SILICON WAFERS AND OXYGEN OUT-DIFFUSION-LESS PROCESS THEREFOR	NI-176017
TW	87105357	1257962	SINGLE CRYSTAL SILICON WAFER AND SINGLE CRYSTAL SILICON INGOT	1257962
TW	88118775	494146	PROCESS FOR GROWING A SINGLE CRYSTAL SILICON INGOT	NI-158475
TW	87105359	577939	LOW DEFECT DENSITY SINGLE CRYSTAL SILICON	NI-197263
TW	87112693	426758	HEAT SHIELD ASSEMBLY AND METHOD OF GROWING VACANCY RICH SINGLE CRYSTAL SILICON	NI-128849
TW	87117066	429272	PROCESS FOR PREPARING A SILICON MELT FROM A POLYSILICON CHARGE	NI-129745

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TW	088109999	1251038	PROCESS AND APPARATUS FOR PREPARATION OF SILICON CRYSTALS WITH REDUCED METAL CONTENT	1251038
TW	87116301	476815	LOW DEFECT DENSITY SINGLE CRYSTAL SILICON	NI-150694
TW	88101499	406176	CRUCIBLE AND METHOD OF PREPARATION THEREOF	NI-121408
TW	88113387	425641	NON-UNIFORM MINORITY CARRIER LIFETIME DISTRIBUTIONS IN HIGH PERFORMANCE SILICON POWER DEVICES	NI-128730
TW	88117745	448248	EPITAXIAL SILICON WAFERS SUBSTANTIALLY FREE OF GROWN-IN DEFECTS	NI-137753
TW	87105351	536562	LOW DEFECT DENSITY SINGLE CRYSTAL SILICON	NI-178963
TW	88117746	467974	SINGLE CRYSTAL SILICON WAFER AND PROCESS FOR PREPARING THE SAME	NI-146406
TW	88115120	434652	THERMALLY ANNEALED WAFERS HAVING IMPROVED INTERNAL GETTERING	NI-131870
TW	89117988	562881	PROCESS FOR PREPARING SINGLE CRYSTAL SILICON HAVING UNIFORM THERMAL HISTORY	NI-190445
TW	88115127	436861	SILICON ON INSULATOR STRUCTURE FROM LOW DEFECT DENSITY SINGLE CRYSTAL SILICON	NI-133267
TW	88115125	439152	NON-OXYGEN PRECIPITATING CZOCHRALSKI SILICON WAFERS	NI-133150
TW	88115126	425636	IDEAL OXYGEN PRECIPITATING SILICON WAFERS AND OXYGEN OUT-DIFFUSION-LESS PROCESS THEREFOR	NI-128169
TW	88121574	1228549	AN EPITAXIAL SILICON WAFER WITH INTRINSIC GETTERING AND A METHOD FOR THE PREPARATION THEREOF	1228549
TW	88110876	473564	PROCESS FOR GROWTH OF DEFECT FREE SILICON CRYSTALS OF ARBITRARILY LARGE DIAMETERS	NI-148903

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TW	89102612	1243217	HEAT SHIELD ASSEMBLY FOR CRYSTAL PULLER	1243217
TW	90115297	527667	METHOD AND APPARATUS FOR FORMING A SILICON WAFER WITH A DENUDED ZONE	NI-175214
TW	90115296	1255874	METHOD AND APPARATUS FOR FORMING AN EPITAXIAL SILICON WAFER WITH A DENUDED ZONE	1255874
TW	088110877	538147	PROCESS FOR PREPARING DEFECT FREE SILICON CRYSTALS WHICH ALLOWS FOR VARIABILITY IN PROCESS CONDITIONS	NI-181056
TW	90126885	583352	METHOD FOR THE PRODUCTION OF LOW DEFECT DENSITY SILICON	NI-199483
TW	090127030	527450	METHOD FOR PREPARING MOLTEN SILICON MELT FROM POLYCRYSTALLINE SILICON CHARGE	NI-175335
TW	89104584	1241365	BARIUM DOPING OF MOLTEN SILICON FOR USE IN CRYSTAL GROWING PROCESS	1241365
TW	89105197	552324	METHOD AND SYSTEM FOR CONTROLLING DIAMETER OF A SILICON CRYSTAL IN A LOCKED SEED LIFT GROWTH PROCESS	NI-186286
TW	89119618	574449	METHOD FOR PRODUCING CZOCHRALSKI SILICON FREE OF AGGLOMERATED SELF-INTERSTITIAL DEFECTS	NI-194994
TW	89119609	571006	PROCESS FOR SUPPRESSING THE NUCLEATION AND/OR GROWTH OF INTERSTITIAL TYPE DEFECTS BY CONTROLLING THE COOLING RATE THROUGH NUCLEATION	NI-193750
TW	90126884	554092	PROCESS FOR PREPARING LOW DEFECT DENSITY SILICON USING HIGH GROWTH RATES	NI-186061
TW	090110944	1285936	MODIFIED SUSCEPTOR FOR USE IN CHEMICAL VAPOR DEPOSITION PROCESS	1285936
TW	90110954	535218	AN EPITAXIAL SILICON WAFER FREE FROM AUTODOPING AND BACKSIDE HALO AND A METHOD AND APPARATUS FOR THE PREPARATION THEREOF	NI-178684
US	14/045325	2014-0096793	UV TREATMENT OF POLISHED WAFERS	

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US	11/968381	2008-0099717	SILICON WAFER ETCHING COMPOSITIONS	7938982
US	11/753722	2007-0227442	CONTROLLING MELT-SOLID INTERFACE SHAPE OF A GROWING SILICON CRYSTAL USING A VARIABLE MAGNETIC FIELD	7611580
US	12/347336	2009-0130824	ARSENIC AND PHOSPHORUS DOPED SILICON WAFER SUBSTRATES HAVING INTRINSIC GATTERING	8026145
US	12/899262	2011-0101504	METHODS OF GRINDING SEMICONDUCTOR WAFERS HAVING IMPROVED NANOTOPOLOGY	8287745
US	11/750706	2007-0266929	CONTROLLING AGGLOMERATED POINT DEFECT AND OXYGEN CLUSTER FORMATION INDUCED BY THE LATERAL SURFACE OF A SILICON SINGLE CRYSTAL DURING CZ GROWTH	8216362
US	11/750717	2007-0269361	SILICON MATERIAL WITH CONTROLLED AGGLOMERATED POINT DEFECTS AND OXYGEN CLUSTERS INDUCED BY THE LATERAL SURFACE	8673248
US	11/960236	2008-0160788	METHODS FOR PRODUCING SMOOTH WAFERS	8058173
US	12/631929	2010-0087123	METHOD FOR ASSESSING WORKPIECE NANOTOPOLOGY USING A DOUBLE SIDE WAFER GRINDER	7927185
US	11/771495	2008-0009231	DRESSING A WAFER POLISHING PAD	7846006
US	12/351290	2009-0176441	SYSTEM AND METHOD FOR DRESSING A WAFER POLISHING PAD	7846007
US	12/454512	2009-0233428	METHODS FOR PREPARING A SEMICONDUCTOR STRUCTURE FOR USE IN BACKSIDE ILLUMINATION APPLICATIONS	8080482
US	13/199587	2011-0318912	METHODS FOR PREPARING A SEMICONDUCTOR WAFER WITH HIGH THERMAL CONDUCTIVITY	
US	10/465528	2004-0255847	FLUID SEALING SYSTEM FOR A CRYSTAL PULLER	6942733
US	13/061386	2011-0163313	FLATTENING PROCESS FOR SEMICONDUCTOR WAFERS	

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US	12/415551	2009-0247055	METHODS FOR ETCHING THE EDGE OF A SILICON WAFER	8309464
US	12/415274	2009-0242126	EDGE ETCHING APPARATUS FOR ETCHING THE EDGE OF A SILICON WAFER	
US	12/415555	2009-0246444	EDGE ETCHED SILICON WAFERS	8192822
US	12/964143		PROCESS FOR ANNEALING SEMICONDUCTOR WAFERS WITH FLAT DOPANT DEPTH PROFILES	8153538
US	11/965521	2009-0166719	EPITAXIAL BARREL SUSCEPTOR HAVING IMPROVED THICKNESS UNIFORMITY	8404049
US	11/967743	2008-0166948	NANOTOPOGRAPHY CONTROL AND OPTIMIZATION USING FEEDBACK FROM WARP DATA	7930058
US	12/891357	2011-0045740	METHODS AND SYSTEMS FOR ADJUSTING OPERATION OF A WAFER GRINDER USING FEEDBACK FROM WARP DATA	8145342
US	12/211516	2010-0066696	WAFER HOLDER FOR SUPPORTING A SEMICONDUCTOR WAFER DURING A THERMAL TREATMENT PROCESS	8186661
US	12/197669		METHOD AND DEVICE FOR CONTINUOUSLY MEASURING SILICON ISLAND ELEVATION	7573587
US	12/108923	2009-0266294	METHOD AND DEVICE FOR FEEDING ARSENIC DOPANT INTO A SILICON CRYSTAL GROWING APPARATUS	7922817
US	12/625931	2010-0132829	METHOD FOR FEEDING ARSENIC DOPANT INTO A SILICON CRYSTAL GROWING APPARATUS	8696811
US	12/493766	2009-0320743	CONTROLLING A MELT-SOLID INTERFACE SHAPE OF A GROWING SILICON CRYSTAL USING AN UNBALANCED MAGNETIC FIELD AND ISO-ROTATION	8398765
US	12/165048	2009-0321372	LOW THERMAL MASS SEMICONDUCTOR WAFER SUPPORT	8042697
US	13/232684	2012-0077138	LOW THERMAL MASS SEMICONDUCTOR WAFER BOAT	8220647

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US	13/232676	2012-0074081	LOW THERMAL MASS SEMICONDUCTOR WAFER PLATE	8220646
US	12/537066	2010-0031870	GENERATING A PUMPING FORCE IN A SILICON MELT BY APPLYING A TIME-VARYING MAGNETIC FIELD	8,551,247
US	13/130160	2011-0223741	METHOD AND SYSTEM FOR STRIPPING THE EDGE OF A SEMICONDUCTOR WAFER	
US	12/726957	2010-0242836	SYSTEMS FOR WEIGHING A PULLED OBJECT	8691008
US	12/726973	2010-0242625	SYSTEMS FOR WEIGHING A PULLED OBJECT HAVING A CHANGING WEIGHT	8347740
US	12/971788	2011-0159668	METHODS FOR PROCESSING SILICON ON INSULATOR WAFERS	8080464
US	12/840549	2011-0017230	METHOD AND SYSTEM FOR PROCESSING ABRASIVE SLURRY	
US	13/733468	2013-0118091	METHODS FOR PROCESSING ABRASIVE SLURRY	
US	13/733499	2013-0118962	SYSTEMS FOR PROCESSING ABRASIVE SLURRY	
US	12/974772	2011-0159665	METHOD FOR THE PREPARATION OF A MULTI-LAYERED CRYSTALLINE STRUCTURE	8367519
US	13/730011	2013-0137241	METHOD FOR THE PREPARATION OF A MULTI-LAYERED CRYSTALLINE STRUCTURE	
US	12/648613	2011-0160890	METHODS FOR GENERATING REPRESENTATIONS OF FLATNESS DEFECTS ON WAFERS	8165706
US	12/648620	2011-0160891	SYSTEMS FOR GENERATING REPRESENTATIONS OF FLATNESS DEFECTS ON WAFERS	8340801
US	12/970139	2011-0151592	METHODS FOR MONITORING THE AMOUNT OF CONTAMINATION IMPARTED INTO SEMICONDUCTOR WAFERS DURING WAFER PROCESSING	8143078

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US	13/353142	2012-0115258	METHODS FOR MONITORING THE AMOUNT OF METAL CONTAMINATION IN A PROCESS	
US	13/021467	2011-0207246	METHODS FOR REDUCING THE WIDTH OF THE UNBONDED REGION IN SOI STRUCTURES	8440541
US	13/021443	2011-0204471	SEMICONDUCTOR WAFERS WITH REDUCED ROLL-OFF AND BONDED AND UNBONDED SOI STRUCTURES PRODUCED FROM SAME	8330245
US	12/847011	2012-0025353	SEMICONDUCTOR AND SOLAR WAFERS	8310031
US	13/049536	2011-0237160	Hydrostatic Pad Pressure Modulation in a Simultaneous Double Side Wafer Grinder	8712575
US	13/162122	2012-0003814	METHODS FOR IN-SITU PASSIVATION OF SILICON-ON-INSULATOR WAFERS	
US	12/772627	2011-0269316	WAFER SUPPORT RING	8420554
US	13/354788	2012-0193753	METHODS FOR REDUCING THE METAL CONTENT IN THE DEVICE LAYER OF SOI STRUCTURES AND SOI STRUCTURES PRODUCED BY SUCH METHODS	
US	13/237049	2012-0073752	ADAPTER RING FOR SILICON ELECTRODE	
US	13/417934	2013-0062020	SYSTEMS AND METHODS FOR CLEAVING A BONDED WAFER PAIR	
US	13/724050	2013-0174829	METHODS FOR MOUNTING AN INGOT ON A WIRE SAW	
US	13/443074	2013-0263779	SUSCEPTOR FOR IMPROVED EPITAXIAL WAFER FLATNESS	
US	13/443076	2013-0263776	METHODS FOR FABRICATING A SEMICONDUCTOR WAFER PROCESSING DEVICE	
US	13/419139	2012-0238070	METHODS FOR PRODUCING SILICON ON INSULATOR STRUCTURES HAVING HIGH RESISTIVITY REGIONS IN THE HANDLE WAFER	

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US	13/663038	2013-0105538	METHODS FOR CLEAVING A BONDED WAFER STRUCTURE	
US	13/663073	2013-0105539	CLAMPING APPARATUS FOR CLEAVING A BONDED WAFER STRUCTURE	
US	13/299926	2013-0125587	METHODS FOR PRODUCING CRUCIBLES WITH A REDUCED AMOUNT OF BUBBLES	
US	13/299922	2013-0129921	METHODS FOR PRODUCING CRUCIBLES WITH A REDUCED AMOUNT OF BUBBLES	8524319
US	13/299929	2013-0125719	PROCESSES FOR PRODUCING SILICON INGOTS	
US	13/299917	2013-0129973	CRUCIBLES WITH A REDUCED AMOUNT OF BUBBLES AND INGOTS AND WAFERS PRODUCED BY USE OF SUCH CRUCIBLES	
US	13/413284	2013-0237032	METHOD OF MANUFACTURING SILICON-ON-INSULATOR WAFERS	
US	13/712561	2013-0176454	AIR POCKET DETECTION METHODS AND SYSTEMS	
US	13/712592	2013-0179094	SYMMETRY BASED AIR POCKET DETECTION METHODS AND SYSTEMS	
US	13/838284	2013-0276695	SUSCEPTOR ASSEMBLIES FOR SUPPORTING WAFERS IN A REACTOR APPARATUS	
US	10/615127	2005-0005841	PROCESS FOR PREPARING A STABILIZED IDEAL OXYGEN PRECIPITATING SILICON WAFER	6955718
US	10/699038	2004-0118333	PROCESS FOR PREPARING SINGLE CRYSTAL SILICON USING CRUCIBLE ROTATION TO CONTROL TEMPERATURE GRADIENT	7125450
US	11/753294	2007-0224783	PROCESS FOR FORMING LOW DEFECT DENSITY, IDEAL OXYGEN PRECIPITATING SILICON	7442253
US	11/763043	2007-0238266	NON-UNIFORM MINORITY CARRIER LIFETIME DISTRIBUTIONS IN HIGH PERFORMANCE SILICON POWER DEVICES	7518879

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US	09/503566		PROCESS FOR PRODUCING A SILICON MELT	6344083
US	09/943600	2002-0020339	PROCESS FOR PREPARING A SILICON MELT	6652645
US	10/036875	2002-0083887	PROCESS FOR PRODUCING A SILICON MELT	6749683
US	09/684266		HEAT SHIELD ASSEMBLY FOR CRYSTAL PULLING APPARATUS	6482263
US	10/113378	2002-0174828	THERMAL ANNEALING PROCESS FOR PRODUCING SILICON WAFERS WITH IMPROVED SURFACE CHARACTERISTICS	6743495
US	09/751897	2002-0084566	SEMICONDUCTOR WAFER HOLDER	6497403
US	10/204654	2003-0209186	CONTROLLED NECK GROWTH PROCESS FOR SINGLE CRYSTAL SILICON	6869477
US	10/039196	2002-0121238	SINGLE CRYSTAL SILICON HAVING IMPROVED GATE OXIDE INTEGRITY	6986925
US	11/089102	2005-0160967	PROCESS FOR PREPARING SINGLE CRYSTAL SILICON HAVING IMPROVED GATE OXIDE INTEGRITY	7431765
US	10/120714	2003-0054841	CONTROL OF OXYGEN PRECIPITATE FORMATION IN HIGH RESISTIVITY CZ SILICON	6897084
US	11/082267	2005-0158969	METHOD FOR CONTROLLING OF THERMAL DONOR FORMATION IN HIGH RESISTIVITY CZ SILICON	7135351
US	10/035456	2003-0077128	GRANULAR SEMICONDUCTOR MATERIAL TRANSPORT SYSTEM AND PROCESS	6609870
US	10/281632	2003-0079673	SEED CRYSTALS FOR PULLING SINGLE CRYSTAL SILICON	6866713
US	10/380806	2004-0009111	NITROGEN-DOPED SILICON SUBSTANTIALLY FREE OF OXIDATION INDUCED STACKING FAULTS	7182809

Crty	App Number	Pub Number	Title	Patent Number
US	11/623142	2007-0169683	NITROGEN-DOPED SILICON SUBSTANTIALLY FREE OF OXIDATION INDUCED STACKING FAULTS	7404856
US	09/892002	2002-0196045	CRYSTAL PULLER AND METHOD FOR GROWING MONOCRYSTALLINE SILICON INGOTS	6663709
US	10/254945	2003-0024473	CRYSTAL PULLER FOR GROWING MONOCRYSTALLINE SILICON INGOTS	6554898
US	10/054629	2002-0100410	LOW DEFECT DENSITY SILICON HAVING A VACANCY-DOMINATED CORE SUBSTANTIALLY FREE OF OXIDATION INDUCED STACKING FAULTS	6846539
US	11/005987	2005-0150445	LOW DEFECT DENSITY SILICON HAVING A VACANCY-DOMINATED CORE SUBSTANTIALLY FREE OF OXIDATION INDUCED STACKING FAULTS	7217320
US	10/256759	2003-0061985	SINGLE CRYSTAL SILICON INGOT HAVING A HIGH ARSENIC CONCENTRATION	7132091
US	10/328481	2003-0136961	SILICON WAFERS WITH STABILIZED OXYGEN PRECIPITATE NUCLEATION CENTERS AND PROCESS FOR MAKING THE SAME	6808781
US	10/963340	2005-0048247	PROCESS FOR MAKING SILICON WAFERS WITH STABILIZED OXYGEN PRECIPITATE NUCLEATION CENTERS	7201800
US	09/928559	2002-0052064	METHOD AND APPARATUS FOR PROCESSING A SEMICONDUCTOR WAFER USING NOVEL FINAL POLISHING METHOD	6709981
US	09/682677	2003-0068958	POLISHING APPARATUS, POLISHING HEAD AND METHOD	6712673
US	10/177444	2003-0008435	SILICON ON INSULATOR STRUCTURE HAVING AN EPITAXIAL LAYER AND INTRINSIC GETTERING	6930375
US	11/174908	2005-0256671	PROCESS FOR PRODUCING SILICON ON INSULATOR STRUCTURE HAVING INTRINSIC GETTERING BY ION IMPLANTATION	7071080
US	10/705813	2004-0112277	CRYSTAL PULLER AND METHOD FOR GROWING A MONOCRYSTALLINE INGOT	8147613
US	10/623967	2005-0016443	METHOD TO MONITOR AND CONTROL THE CRYSTAL COOLING OR QUENCHING RATE BY MEASURING CRYSTAL SURFACE TEMPERATURE	6960254

City	App Number	Pub Number	Title	Patent Number
US	10/442900	2004-0235402	WAFER CARRIER	7008308
US	11/152362	2006-0011588	SILICON WAFER ETCHING PROCESS AND COMPOSITION	7323421
US	10/898148	2006-0016389	PARTIALLY DEVITRIFIED CRUCIBLE	7497907
US	10/840854	2005-0250297	PROCESS FOR METALLIC CONTAMINATION REDUCTION IN SILICON WAFERS	7084048
US	11/026780	2006-0144321	CONTROLLING MELT-SOLID INTERFACE SHAPE OF A GROWING SILICON CRYSTAL USING A VARIABLE MAGNETIC FIELD	7223304
US	10/930654	2005-0279277	SYSTEMS AND METHODS FOR MEASURING AND REDUCING DUST IN GRANULAR MATERIAL	7291222
US	11/270790	2007-0105279	ARSENIC AND PHOSPHORUS DOPED SILICON WAFER SUBSTRATES HAVING INTRINSIC GETTERING	7485928
US	11/436688	2006-0263967	HIGH RESISTIVITY SILICON STRUCTURE AND A PROCESS FOR THE PREPARATION THEREOF	7521382
US	11/155385	2005-0279278	MELTER ASSEMBLY AND METHOD FOR CHARGING A CRYSTAL FORMING APPARATUS WITH MOLTEN SOURCE MATERIAL	7691199
US	11/155105	2005-0279276	MELTER ASSEMBLY AND METHOD FOR CHARGING A CRYSTAL FORMING APPARATUS WITH MOLTEN SOURCE MATERIAL	7344594
US	11/155104	2005-0279275	MELTER ASSEMBLY AND METHOD FOR CHARGING A CRYSTAL FORMING APPARATUS WITH MOLTEN SOURCE MATERIAL	7465351
US	11/027360	2006-0144320	ELECTROMAGNETIC PUMPING OF LIQUID SILICON IN A CRYSTAL GROWING PROCESS	7291221
US	10/598851	2008-0020684	WAFER CLAMPING DEVICE FOR A DOUBLE SIDE GRINDER	8066553
US	10/900938	2006-0024969	HIGH PURITY SILICON CARBIDE STRUCTURES	7888685

CRY	App Number	Pub Number	Title	Patent Number
US	11/755472	2007-0221609	METHOD FOR PURIFYING SILICON CARBIDE COATED STRUCTURES	7696103
US	11/041693		SEMICONDUCTOR WAFER BOAT FOR A VERTICAL FURNACE	7033168
US	11/107444	2006-0231035	MODIFIED SUSCEPTOR FOR BARREL REACTOR	7462246
US	11/621920	2007-0178807	WIRE SAW INGOT SLICING SYSTEM AND METHOD WITH INGOT PREHEATING, WEB PREHEATING, SLURRY TEMPERATURE CONTROL AND/OR SLURRY FLOW RATE CONTROL	7878883
US	11/408503	2007-0249136	SILICON STRUCTURES WITH IMPROVED RESISTANCE TO RADIATION EVENTS	7568951
US	11/617430	2007-0179659	DOUBLE SIDE WAFER GRINDER AND METHODS FOR ASSESSING WORKPIECE NANOTOPOLOGY	7662023
US	11/614129	2008-0153391	METHOD OF POLISHING A SEMICONDUCTOR WAFER	7559825
US	11/617433	2007-0179660	DOUBLE SIDE WAFER GRINDER AND METHODS FOR ASSESSING WORKPIECE NANOTOPOLOGY	7601049
US	11/967694	2009-0169346	SEMICONDUCTOR WAFER CARRIER BLADE	7878562
US	12/130190	2009-0298399	SEMICONDUCTOR WAFER POLISHING APPARATUS AND METHOD OF POLISHING	8192248
US	08/245592		METHOD OF ROUGH POLISHING SEMICONDUCTOR WAFERS TO REDUCE SURFACE ROUGHNESS	5571373
US	08/739550		GETTERING AGENT	5855859
US	08/242560		SEMICONDUCTOR WAFER POLISHING APPARATUS AND METHOD	5605487
US	08/283782		METHOD FOR ETCHING A SEMICONDUCTOR MATERIAL WITHOUT ALTERING FLOW PATTERN DEFECT DISTRIBUTION	5573680

Ctry	App Number	Pub Number	Title	Patent Number
US	08/490465		SURFACE-TREATED CRUCIBLES FOR IMPROVED ZERO DISLOCATION PERFORMANCE PROCESS FOR THE PREPARATION OF SILICON WAFERS HAVING A CONTROLLED DISTRIBUTION OF OXYGEN PRECIPITATE NUCLEATION CENTERS	5976247
US	08/934946		METHODS FOR IMPROVING ZERO DISLOCATION YIELD OF SINGLE CRYSTALS	5892989
US	08/490473		SILICON SINGLE CRYSTAL HAVING ELIMINATED DISLOCATION IN ITS NECK	5980629
US	08/483304		APPARATUS FOR CONTROLLING NUCLEATION OF OXYGEN PRECIPITATES IN SILICON CRYSTALS	5578284
US	08/589612		METHOD FOR CONTROLLING GROWTH OF A SILICON CRYSTAL	5840120
US	08/459765		NON-DISTORTING VIDEO CAMERA FOR USE WITH A SYSTEM FOR CONTROLLING GROWTH OF A SILICON CRYSTAL	5663799
US	08/558609		SUSCEPTOR AND BAFFLE THEREFOR	5656078
US	08/423363		METHOD FOR PREPARING MOLTEN SILICON MELT FROM POLYCRYSTALLINE SILICON CHARGE	5518549
US	08/507055		PRECISION CONTROLLED PRECIPITATION OF OXYGEN IN SILICON	5588993
US	08/403301		PROCESS FOR CONTROLLING THE OXYGEN CONTENT IN SILICON WAFERS HEAVILY DOPED WITH ANTIMONY OR ARSENIC	5593494
US	08/732527		APPARATUS FOR CONTROLLING THE OXYGEN CONTENT IN SILICON WAFERS HEAVILY DOPED WITH ANTIMONY OR ARSENIC	5904768
US	09/268968		SIO PROBE FOR REAL-TIME MONITORING AND CONTROL OF OXYGEN DURING CZOCHRALSKI GROWTH OF SINGLE CRYSTAL SILICON	6214109
US	08/711085		RADIANT POLISHING BLOCK HEATER	5795381
US	08/950842			5906533

Qty	App Number	Pub Number	Title	Patent Number
US	08/725861		METHOD FOR ROTATING A CRUCIBLE OF A CRYSTAL PULLING MACHINE	5766341
US	08/488924		APPARATUS FOR ROTATING A CRUCIBLE OF A CRYSTAL PULLING MACHINE	5593498
US	08/530612		METHOD FOR TUNING BARREL REACTOR PURGE SYSTEM	5908504
US	08/689432		METHOD AND APPARATUS FOR CONTROLLING FLATNESS OF POLISHED SEMICONDUCTOR WAFER	5787595
US	08/686570		POLYSILICON PARTICLE CLASSIFYING APPARATUS	5791493
US	08/644181		METHOD AND APPARATUS FOR AIMING A BARREL REACTOR NOZZLE	5843234
US	08/639185		APPARATUS AND METHOD FOR SHAPING POLISHING PADS	5840202
US	08/653666		AUTOMATED WAFER LAPPING SYSTEM	5679055
US	08/595075		METHOD FOR PREPARING MOLTEN SILICON MELT FROM POLYCRYSTALLINE SILICON CHARGE	5814148
US	08/694157		PROCESS FOR CONTROLLING THERMAL HISTORY OF CZOCHRALSKI-GROWN SILICON	5779791
US	08/568997		PRE-THERMAL TREATMENT CLEANING PROCESS	5712198
US	08/686665		COOLING SYSTEM AND METHOD FOR EPITAXIAL BARREL REACTOR	5849076
US	09/030110		IDEAL OXYGEN PRECIPITATING SILICON WAFERS AND OXYGEN OUT-DIFFUSION-LESS PROCESS THEREFOR	6180220
US	09/704893		IDEAL OXYGEN PRECIPITATING SILICON WAFER HAVING AN ASYMMETRICAL VACANCY CONCENTRATION PROFILE AND A PROCESS FOR THE PREPARATION THEREOF	6566068

City	App Number	Pub Number	Title	Patent Number
US	10/430798	2003-0196586	IDEAL OXYGEN PRECIPITATING SILICON WAFERS AND OXYGEN OUT-DIFFUSION-LESS PROCESS THEREFOR	6849119
US	08/710655		CUTTING MACHINE	5827113
US	09/000061		METHOD AND APPARATUS FOR WASHING SILICON INGOT WITH WATER TO REMOVE PARTICULATE MATTER	6006736
US	09/057907		LOW DEFECT DENSITY SILICON	6287380
US	09/057801		LOW DEFECT DENSITY SELF-INTERSTITIAL DOMINATED SILICON	6254672
US	09/475320	2002-0007779	METHOD FOR REVEALING AGGLOMERATED INTRINSIC POINT DEFECTS IN SEMICONDUCTOR CRYSTALS	6638357
US	09/833777	2001-0020437	LOW DEFECT DENSITY SILICON AND A PROCESS FOR PRODUCING LOW DEFECT DENSITY SILICON WHEREIN V/G0 IS CONTROLLED BY CONTROLLING HEAT TRANSFER AT THE MELT/SOLID INTERFACE	6409827
US	09/816015	2001-0025597	LOW DEFECT DENSITY, SELF-INTERSTITIAL DOMINATED SILICON	6409826
US	10/135174	2002-0139294	LOW DEFECT DENSITY REGIONS FOR SELF-INTERSTITIAL DOMINATED SILICON	6805150
US	10/135597	2002-0170485	LOW DEFECT DENSITY EPITAXIAL WAFER AND A PROCESS FOR THE PREPARATION THEREOF	6632278
US	08/907795		NON-DASH NECK METHOD FOR SINGLE CRYSTAL SILICON GROWTH	5885344
US	08/764458		POLISHING BLOCK HEATER	5770522
US	08/675550		PROCESS FOR ELIMINATING DISLOCATIONS IN THE NECK OF A SILICON SINGLE CRYSTAL	5628823
US	08/895388		METHOD AND APPARATUS FOR CUTTING AN INGOT	6006738

City	App Number	Pub Number	Title	Patent Number
US	08/843632		APPARATUS FOR CLEANING SEMICONDUCTOR WAFERS	5816274
US	09/002592		CRYSTAL GROWING APPARATUS WITH MELT-DOPING FACILITY	6019838
US	08/904943		HEAT SHIELD ASSEMBLY AND METHOD OF GROWING VACANCY RICH SINGLE CRYSTAL SILICON	5942032
US	08/970129		APPARATUS FOR CLEANING SEMICONDUCTOR WAFERS	5839460
US	09/003986		IN SITU WAFER CLEANING PROCESS	5990014
US	09/082906		PROCESS FOR THE REMOVAL OF COPPER AND OTHER METALLIC IMPURITIES FROM SILICON	6482269
US	09/356616		METHOD OF PROCESSING SEMICONDUCTOR WAFERS	6114245
US	08/863960		SECONDARY EDGE REFLECTOR FOR HORIZONTAL REACTOR	5792273
US	08/941777		WAFER DEMOUNT APPARATUS	5865670
US	09/691994		ELECTRICAL RESISTANCE HEATER AND METHOD FOR CRYSTAL GROWING APPARATUS	6503322
US	09/092391		ELECTRICAL HEATER FOR CRYSTAL GROWTH APPARATUS WITH UPPER SECTIONS PRODUCING INCREASED HEATING POWER COMPARED TO LOWER SECTIONS	6093913
US	08/990123		POST-LAPPING CLEANING PROCESS FOR SILICON WAFERS	5837662
US	08/951264		PROCESS FOR PREPARING A SILICON MELT FROM A POLYSILICON CHARGE	5919303
US	09/093520		COLLECTOR FOR AN AUTOMATED ON-LINE BATH ANALYSIS SYSTEM	6210640

City	App Number	Pub Number	Title	Patent Number
US	08/940166		HEAT SHIELD FOR CRYSTAL PULLER	5922127
US	09/234144		HEAT SHIELD FOR CRYSTAL PULLER	6053974
US	09/097779		PROCESS AND APPARATUS FOR PREPARATION OF SILICON CRYSTALS WITH REDUCED METAL CONTENT	6183653
US	09/072564		INJECTOR FOR REACTOR	5891250
US	09/057800		LOW DEFECT DENSITY, IDEAL OXYGEN PRECIPITATING SILICON	6190631
US	09/705092		PROCESS FOR PRODUCING LOW DEFECT DENSITY, IDEAL OXYGEN PRECIPITATING SILICON	6555194
US	10/373899	2004-0025782	PROCESS FOR PRODUCING LOW DEFECT DENSITY, IDEAL OXYGEN PRECIPITATING SILICON	6896728
US	11/058996	2005-0170610	LOW DEFECT DENSITY, IDEAL OXYGEN PRECIPITATING SILICON	7229693
US	09/017942		CRUCIBLE AND METHOD OF PREPARATION THEREOF	5913975
US	09/107728		SUSCEPTOR FOR BARREL REACTOR	6129048
US	09/677909		RADIO FREQUENCY IDENTIFICATION SYSTEM AND METHOD FOR TRACKING SILICON WAFERS	6330971
US	09/245238		TUNGSTEN DOPED CRUCIBLE AND METHOD FOR PREPARING SAME	6187089
US	09/366850		NON-UNIFORM MINORITY CARRIER LIFETIME DISTRIBUTIONS IN HIGH PERFORMANCE SILICON POWER DEVICES	6828690
US	10/911965	2005-0006796	PROCESS FOR MAKING NON-UNIFORM MINORITY CARRIER LIFETIME DISTRIBUTION IN HIGH PERFORMANCE SILICON POWER DEVICES	7242037

City	App Number	Pub Number	Title	Patent Number
US	09/172546		METHOD AND SYSTEM FOR CONTROLLING GROWTH OF A SILICON CRYSTAL	6171391
US	09/417610		EPITAXIAL SILICON WAFERS SUBSTANTIALLY FREE OF GROWN-IN DEFECTS	6284039
US	09/874487	2001-0039916	EPITAXIAL WAFER SUBSTANTIALLY FREE OF GROWN-IN DEFECTS	6566649
US	10/441413	2003-0206191	SINGLE CRYSTAL SILICON WAFER HAVING AN EPITAXIAL LAYER SUBSTANTIALLY FREE FROM GROWN-IN DEFECTS	7097718
US	09/167747		CONTINUOUS OXIDATION PROCESS FOR CRYSTAL PULLING APPARATUS	6039801
US	09/489481		CONTINUOUS OXIDATION PROCESS FOR CRYSTAL PULLING APPARATUS	6315828
US	09/057851		LOW DEFECT DENSITY VACANCY DOMINATED SILICON	5919302
US	09/270366		VACANCY DOMINATED, DEFECT-FREE SILICON	6379642
US	10/000545	2002-0078880	VACANCY, DOMINATED, DEFECT-FREE SILICON	6840997
US	09/404428		METHOD OF PROCESSING SEMICONDUCTOR WAFERS TO BUILD IN BACK SURFACE DAMAGE	6214704
US	09/416998		THERMALLY ANNEALED, LOW DEFECT DENSITY SINGLE CRYSTAL SILICON	6416836
US	10/073506	2002-0083889	THERMAL ANNEALING PROCESS FOR PRODUCING LOW DEFECT DENSITY SINGLE CRYSTAL SILICON	6743289
US	09/385108		THERMALLY ANNEALED WAFERS HAVING IMPROVED INTERNAL GETTERING	6361619

City	App Number	Pub Number	Title	Patent Number
US	10/067070	2002-0170631	PROCESS FOR PRODUCING THERMALLY ANNEALED WAFERS HAVING IMPROVED INTERNAL GETTERING	6686260
US	09/276278		METHOD FOR PROCESSING A SEMICONDUCTOR WAFER	6227944
US	09/352980		PROCESS FOR FABRICATING SEMICONDUCTOR WAFERS WITH EXTERNAL GETTERING	6338805
US	09/596493		PROCESS FOR PREPARING SINGLE CRYSTAL SILICON HAVING UNIFORM THERMAL HISTORY	6458202
US	09/387288		SILICON ON INSULATOR STRUCTURE FROM LOW DEFECT DENSITY SINGLE CRYSTAL SILICON	6236104
US	09/737715	2001-0030348	SILICON ON INSULATOR STRUCTURE HAVING A LOW DEFECT DENSITY HANDLER WAFER AND PROCESS FOR THE PREPARATION THEREOF	6342725
US	10/038084	2002-0113265	DEVICE LAYER OF A SILICON-ON-INSULATOR STRUCTURE HAVING VACANCY DOMINATED AND SUBSTANTIALLY FREE OF AGGLOMERATED VACANCY-TYPE DEFECTS	6849901
US	09/379383		NON-OXYGEN PRECIPITATING CZOCHRALSKI SILICON WAFERS	6336968
US	09/929585	2002-0000185	PROCESS FOR THE PREPARATION OF NON-OXYGEN PRECIPITATING CZOCHRALSKI SILICON WAFERS	6432197
US	10/217703	2002-0189528	PROCESS FOR SUPPRESSING OXYGEN PRECIPITATION IN VACANCY DOMINATED SILICON	6709511
US	09/384669		PROCESS FOR PREPARING AN IDEAL OXYGEN PRECIPITATING SILICON WAFER	6191010
US	09/704900		PROCESS FOR THE PREPARATION OF AN IDEAL OXYGEN PRECIPITATING SILICON WAFER HAVING AN ASYMMETRICAL VACANCY CONCENTRATION PROFILE CAPABLE OF FORMING AN ENHANCED DENUDED ZONE	6579779

City	App Number	Pub Number	Title	Patent Number
US	10/460901	2003-0221609	PROCESS FOR THE PREPARATION OF AN IDEAL OXYGEN PRECIPITATING SILICON WAFER CAPABLE OF FORMING AN ENHANCED DENUDED ZONE	6713370
US	09/250908		EPITAXIAL SILICON WAFER WITH INTRINSIC GETTERING	6284384
US	09/859094	2001-0032581	EPITAXIAL SILICON WAFER WITH INTRINSIC GETTERING AND A METHOD FOR THE PREPARATION THEREOF	6537655
US	10/400594	2005-0098092	EPITAXIAL SILICON WAFER WITH INTRINSIC GETTERING AND A METHOD FOR THE PREPARATION THEREOF	6958092
US	09/607391		METHOD AND APPARATUS FOR FORMING A SILICON WAFER WITH A DENUDED ZONE	6599815
US	09/344709	2001-0008114	PROCESS FOR GROWTH OF DEFECT FREE SILICON CRYSTALS OR ARBITRARILY LARGE DIAMETERS	6328795
US	10/035540	2002-0092460	PROCESS FOR GROWING DEFECT-FREE SILICON WHEREIN THE GROWN SILICON IS COOLED IN A SEPARATE CHAMBER	6562123
US	10/437141	2004-0003770	PROCESS FOR COOLING A SILICON INGOT HAVING A VACANCY DOMINATED REGION TO PRODUCE DEFECT FREE SILICON	6913647
US	09/258478		HEAT SHIELD ASSEMBLY FOR CRYSTAL PULLER	6197111
US	09/607389	2002-0078882	METHOD AND APPARATUS FOR FORMING AN EPITAXIAL SILICON WAFER WITH A DENUDED ZONE	6339016

City	App Number	Pub Number	Title	Patent Number
US	09/344036	2001-0003268	PROCESS FOR PREPARING DEFECT FREE SILICON CRYSTALS WHICH ALLOWS FOR VARIABILITY IN PROCESS CONDITIONS	6312516
US	09/853232	2001-0027743	PROCESS FOR GROWING SILICON CRYSTALS WHICH ALLOWS FOR VARIABILITY IN THE PROCESS CONDITIONS WHILE SUPPRESSING THE FORMATION OF AGGLOMERATED INTRINSIC POINT DEFECTS	6500255
US	10/260239	2003-0116081	PROCESS FOR GROWING A SILICON CRYSTAL SEGMENT SUBSTANTIALLY FREE FROM AGGLOMERATED INTRINSIC POINT DEFECTS WHICH ALLOWS FOR VARIABILITY IN THE PROCESS CONDITIONS	6652646
US	09/807907		CARRIER FOR CLEANING SILICON WAFERS	6520191
US	09/972608	2002-0056410	METHOD FOR THE PRODUCTION OF LOW DEFECT DENSITY SILICON	6668307
US	10/008812	2002-0043206	METHOD FOR CONTROLLING GROWTH OF A SILICON CRYSTAL TO MINIMIZE GROWTH RATE AND DIAMETER DEVIATIONS	6726764
US	10/022967	2002-0086539	PROCESS FOR RECLAIMING SEMICONDUCTOR WAFERS AND RECLAIMED WAFERS	7008874
US	09/521525		STRONTIUM DOPING OF MOLTEN SILICON FOR USE IN CRYSTAL GROWING PROCESS	6360312

City	App Number	Pub Number	Title	Patent Number
US	09/521288		BARIUM DOPING OF MOLTEN SILICON FOR USE IN CRYSTAL GROWING PROCESS	6319313
US	09/502340		METHOD AND APPARATUS FOR CONTROLLING DIAMETER OF A SILICON CRYSTAL IN A LOCKED SEED LIFT GROWTH PROCESS	6776840
US	09/507811		METHOD FOR WAFER PROCESSING	6514423
US	09/481080	2002-0004305	SEMICONDUCTOR WAFER MANUFACTURING PROCESS	6376395
US	09/661821		METHOD FOR PRODUCING CZOCHRALSKI SILICON FREE OF AGGLOMERATED SELF-INTERSTITIAL DEFECTS	6635587
US	09/871255	2002-0053315	PROCESS FOR PREPARING LOW DEFECT DENSITY SILICON USING HIGH GROWTH RATES	6689209
US	09/432928		METHOD OF DETERMINING PERFORMANCE CHARACTERISTICS OF POLISHING PADS	6293139
US	09/506105		SEMICONDUCTOR WAFER MANUFACTURING PROCESS	6376335
US	09/608304		NON-CONTAMINATING GAS-TIGHT VALVE FOR SEMICONDUCTOR APPLICATIONS	6435474
US	09/421187		METHOD OF CONTROLLING GROWTH OF A SEMICONDUCTOR CRYSTAL TO AUTOMATICALLY TRANSITION FROM TAPER GROWTH TO TARGET DIAMETER GROWTH	6203611

City	App Number	Pub Number	Title	Patent Number
US	09/815508	2002-0134302	HEAT SHIELD ASSEMBLY FOR CRYSTAL PULLER	6579362
US	09/505269		PROCESS FOR REDUCING SURFACE VARIATIONS FOR POLISHED WAFER	6479386
US	09/566890		MODIFIED SUSCEPTOR FOR USE IN CHEMICAL VAPOR DEPOSITION PROCESS	6444027
US	10/229415	2003-0041799	MODIFIED SUSCEPTOR FOR USE IN CHEMICAL VAPOR DEPOSITION PROCESS	6652650
US	09/723847		DEFECT CLASSIFICATION USING SCATTERED LIGHT INTENSITIES	6515742
US	09/752222	2001-0037761	EPITAXIAL SILICON WAFER FREE FROM AUTODOPING AND BACKSIDE HALO AND A METHOD AND APPARATUS FOR THE PREPARATION THEREOF	6596095
US	13/432326	2012-0247686	SYSTEMS AND METHODS FOR ULTRASONICALLY CLEAVING A BONDED WAFER PAIR	
US	13/890316	2013-0240830	DIRECT AND SEQUENTIAL FORMATION OF MONOLAYERS OF BORON NITRIDE AND GRAPHENE ON SUBSTRATES	
WO	PCT/US2011/056428	WO 2013/055368	METHOD TO DELINEATE CRYSTAL RELATED DEFECTS	
WO	PCT/US2012/071715	WO 2013/101872	METHODS FOR MOUNTING AN INGOT ON A WIRE SAW	
WO	PCT/US2013/035777		SUSCEPTOR FOR IMPROVED EPITAXIAL WAFER FLATNESS AND METHODS FOR FABRICATING A SEMICONDUCTOR WAFER PROCESSING DEVICE	

City	App Number	Pub Number	Title	Patent Number
WO	PCT/US2012/028920	WO 2012/125632	SILICON ON INSULATOR STRUCTURES HAVING HIGH RESISTIVITY REGIONS IN THE HANDLE WAFER AND METHODS FOR PRODUCING SUCH STRUCTURES	
WO	PCT/US2012/062194	WO 2013/066758	CLAMPING APPARATUS FOR CLEAVING A BONDED WAFER STRUCTURE AND METHODS FOR CLEAVING	
WO	PCT/US2012/065208	WO 2013/074743	CRUCIBLES WITH A REDUCED AMOUNT OF BUBBLES, INGOTS AND WAFERS PRODUCED BY USE OF SUCH CRUCIBLES AND RELATED METHODS	
WO	PCT/US2013/027794		A METHOD OF MANUFACTURING SILICON-ON-INSULATOR WAFERS	
WO	PCT/US2013/023046	WO 2013/112779	QUALITATIVE CRYSTAL DEFECT EVALUATION METHOD	
WO	PCT/US2012/070169	WO 2013/101527	AIR POCKET DETECTION METHODS AND SYSTEMS	
WO	PCT/US2013/036381		SUSCEPTOR ASSEMBLIES FOR SUPPORTING WAFERS IN A REACTOR APPARATUS	

UNPUBLISHED PATENTS

SunEdison Semiconductor Limited holds an additional 174 pending and unpublished Patents.

JOINTLY OWNED / LICENSED PATENTS

The 37 Patents listed below are either jointly-owned with, or subject to a license in favor of, a third party.

CH	998302066.5	0968801	SYSTEM TO SEPARATE, REGENERATE AND REUSE EXHAUSTED GLYCOL BASED SLURRY	0968801
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City	App Number	Pub Number	Title	Patent Number
CN	98808456.2	1268194	METHOD AND SYSTEM FOR CONTROLLING GROWTH OF A SILICON CRYSTAL	ZL98808456.2
CN	98809673.0	1272147	METHOD FOR CONTROLLING GROWTH OF A SILICON CRYSTAL	ZL98809673.0
CN	99808051.9	CN1307517	METHOD FOR THE SEPARATION, REGENERATION AND REUSE OF AN EXHAUSTED GLYCOL-BASED SLURRY	ZL99808051.9
DE	98935581.3	1002144	METHOD AND SYSTEM FOR CONTROLLING GROWTH OF A SILICON CRYSTAL	1002144
DE	98950721.5	1019567	METHOD FOR CONTROLLING GROWTH OF A SILICON CRYSTAL	69802557.1
DE	99830266.5	0988801	SYSTEM TO SEPARATE, REGENERATE AND REUSE EXHAUSTED GLYCOL BASED SLURRY	DE69904986
FR	98935581.3	1002144	METHOD AND SYSTEM FOR CONTROLLING GROWTH OF A SILICON CRYSTAL	1002144
FR	98950721.5	1019567	METHOD FOR CONTROLLING GROWTH OF A SILICON CRYSTAL	1019567
GB	98950721.5	1019567	METHOD AND SYSTEM FOR CONTROLLING GROWTH OF A SILICON CRYSTAL	1019567
IT	98935581.3	1002144	METHOD AND SYSTEM FOR CONTROLLING GROWTH OF A SILICON CRYSTAL	1002144
IT	98950721.5	1019567	METHOD FOR CONTROLLING GROWTH OF A SILICON CRYSTAL	1019567
IT	RM98A000439		SYSTEM TO SEPARATE, REGENERATE AND REUSE EXHAUSTED GLYCOL BASED SLURRY	1299540
JP	2000-503267	2001-510141	METHOD AND SYSTEM FOR CONTROLLING GROWTH OF A SILICON CRYSTAL	4253117

City	App Number	Pub Number	Title	Patent Number
JP	2000-513996	2001-518443A	METHOD AND SYSTEM FOR CONTROLLING GROWTH OF A SILICON CRYSTAL	4253123
JP	2000-557946	2002-519209A	SYSTEM TO SEPARATE, REGENERATE AND REUSE EXHAUSTED GLYCOL BASED SLURRY	4369054
KR	7000395/2000		METHOD AND SYSTEM FOR CONTROLLING GROWTH OF A SILICON CRYSTAL	491392
MY	PI 98003250		METHOD AND SYSTEM FOR CONTROLLING GROWTH OF A SILICON CRYSTAL	MY-118719-A
MY	PI 98004451		METHOD AND SYSTEM FOR CONTROLLING GROWTH OF A SILICON CRYSTAL	MY-117326-A
SG	200000053-9		METHOD AND SYSTEM FOR CONTROLLING GROWTH OF A SILICON CRYSTAL	70321
SG	200001324-3		METHOD AND SYSTEM FOR CONTROLLING GROWTH OF A SILICON CRYSTAL	71566
TW	101138780	201320165	DIRECT FORMATION OF GRAPHENE ON SEMICONDUCTOR SUBSTRATES	
TW	87111594	1223679	METHOD AND SYSTEM FOR CONTROLLING GROWTH OF A SILICON CRYSTAL	NI-223679
TW	89106408	1240770	METHOD AND SYSTEM OF CONTROLLING TAPER GROWTH IN A SEMICONDUCTOR CRYSTAL GROWTH PROCESS	1240770
US	13/652665	2013-0099195	DIRECT FORMATION OF GRAPHENE ON SEMICONDUCTOR SUBSTRATES	
US	08/459765		METHOD FOR CONTROLLING GROWTH OF A SILICON CRYSTAL	5653799
US	08/423363		SUSCEPTOR AND BAFFLE THEREFOR	5518549

City	App Number	Pub Number	Title	Patent Number
US	08/896177		METHOD AND SYSTEM FOR CONTROLLING GROWTH OF A SILICON CRYSTAL	5846318
US	08/620137		SYSTEM FOR CONTROLLING GROWTH OF A SILICON CRYSTAL	5665159
US	08/939802		METHOD FOR CONTROLLING GROWTH OF A SILICON CRYSTAL	5882402
US	09/345934		METHOD FOR THE SEPARATION REGENERATION AND REUSE OF AN EXHAUSTED GLYCOL-BASED SLURRY	6231628
US	09/287916		METHOD AND SYSTEM OF CONTROLLING TAPER GROWTH IN A SEMICONDUCTOR CRYSTAL GROWTH PROCESS	6241818
WO	PCT/US2012/060810	WO 2013/059457	DIRECT FORMATION OF GRAPHENE ON SEMICONDUCTOR SUBSTRATES	

**Schedule B
Trademarks**

Trademark	Jurisdiction	Serial No.	Filing Date	Registration No.	Registration Date
ADVANTA	United States of America	78/537,684	12/23/2004	3,116,254	7/18/2006
MAGIC DENUDED ZONE	China (People's Republic)	9800115591	10/13/1998	1423525	7/21/2000
MAGIC DENUDED ZONE	European Community	961243	10/12/1998	961243	3/10/2000
MAGIC DENUDED ZONE	Japan	087955/1998	10/12/1998	4337630	11/19/1999
MAGIC DENUDED ZONE	Korea, Republic of	98-26283	10/9/1998	457911	11/3/1999
MAGIC DENUDED ZONE	Malaysia	98/11864	10/12/1998	98/11864	2/28/2002
MAGIC DENUDED ZONE	Singapore	T98/10369Z	4/15/1998	T98/10369Z	4/15/1998
MAGIC DENUDED ZONE	Taiwan	87049919	10/13/1998	879571	1/16/2000
MAGIC DENUDED ZONE	United States of America	75/468,527	4/15/1998	2,400,584	10/31/2000
MDZ	China (People's Republic)	2000128654	8/23/2000	1772606	5/21/2002
MDZ	European Community	1789767	8/2/2000	1789767	10/17/2001
MDZ	Korea, Republic of	40-2000-35495	7/24/2000	40-0513559	2/26/2002
MDZ	Singapore	11334	6/30/2000	T00/11334I	6/23/2000
MDZ	United States of America	76/076,714	6/23/2000	2,459,810	6/12/2001
MDZ (stylized)	Taiwan	89048194	8/18/2000	963051	10/1/2001
MDZ MAGIC DENUDED ZONE (stylized)	Malaysia	2000/10625	8/3/2000	10625	6/13/2003
MEMC	Australia	867269	2/23/2001	867269	11/20/2001
MEMC	Brazil	823529444	1/26/2001	823529444	3/13/2007
MEMC	Canada	1,091,318	2/1/2001	TMA571,377	11/28/2002
MEMC	China (People's Republic)	970049709	5/23/1997	1209091	9/21/1998
MEMC	European Community	2077733	1/30/2001	2077733	4/12/2002
MEMC	Hong Kong	03034/2001	2/23/2001	2002B16095	12/18/2002
MEMC	Indonesia	2.00104E+12	2/26/2001	IDM000311110	1/10/2002
MEMC	Israel	147239	3/8/2001	147239	2/5/2002
MEMC	Japan	7772/2001	2/1/2001	4550043	3/8/2002
MEMC	Korea, Republic of	3718/2001	2/2/2001	40-0520836	5/20/2002
MEMC	Malaysia	2001-02464	2/28/2001	1002464	3/31/2004
MEMC	Mexico	1160587	3/7/2011	1261901	1/23/2012
MEMC	Norway	2000 12159	10/10/2000	208784	5/31/2001
MEMC	Russian Federation	2001706121	3/1/2001	224225	10/9/2002
MEMC	Singapore	T01/03068D	3/7/2001	T01/03068D	3/7/2001
MEMC	Switzerland	2134/2001	2/28/2001	488193	8/22/2001
MEMC	Taiwan	90006102	2/26/2001	987749	3/1/2002
MEMC	United States of America	76/207,396	2/8/2001	2,506,929	11/13/2001
MEMC - TECHNOLOGY IS BUILT ON US	Norway	2001 01499	1/31/2001	210415	9/13/2001
MEMC IS BUILT ON US	Russian Federation	2001706120	3/1/2001	232068	12/17/2002
MEMC TECHNOLOGY IS BUILT ON US	Australia	867272	2/23/2001	867272	11/20/2001
MEMC TECHNOLOGY IS BUILT ON US	Brazil	823684156	3/23/2001		

Trademark	Jurisdiction	Serial No.	Filing Date	Registration No.	Registration Date
MEMC TECHNOLOGY IS BUILT ON US	Indonesia	2.00104E+12	2/26/2001	IOM000311109	1/10/2002
MEMC TECHNOLOGY IS BUILT ON US	Korea, Republic of	2002-46310	10/9/2002	572397	1/26/2004
MEMC TECHNOLOGY IS BUILT ON US	Malaysia	2001-02463	2/28/2001	1002463	3/31/2004
MEMC TECHNOLOGY IS BUILT ON US	Singapore	T01/030698	3/7/2001	T01/030698	3/7/2001
MEMC TECHNOLOGY IS BUILT ON US	Taiwan	90006823	3/2/2001	1031486	2/1/2003
MEMC-TECHNOLOGY IS BUILT ON US	Japan	37782/2002	5/9/2002	4650702	3/7/2003
OPTIA	United States of America	78/537,640	12/23/2004	3,216,953	3/13/2007
PERFECT SILICON	United States of America	78/537,671	12/23/2004	3,231,772	4/17/2007
PERFECTSOI & design	United States of America	78/537,327	12/22/2004	3,325,895	10/30/2007
TECHNOLOGY IS BUILT ON US	Canada	1,091,319	2/1/2001	603101	2/24/2004
TECHNOLOGY IS BUILT ON US	European Community	2080257	1/30/2001	2080257	2/5/2003
TECHNOLOGY IS BUILT ON US	Mexico	67028	3/7/2011	66980	1/13/2012
TECHNOLOGY IS BUILT ON US	Switzerland	02135/2001	2/28/2001	490590	10/22/2001
TECHNOLOGY IS BUILT ON US	United States of America	76/062,723	6/5/2000	2,526,106	1/1/2002

Schedule C
Copyrights

Jurisdiction	Title of Work	Registration Number	Registration Date
U.S.	Building on the Past, Ready for the Future: A Fiftieth Anniversary Celebration of MEMC Electronic Materials, Inc.	TX0007290780	16-Nov-10
U.S.	ADE cell based recipe management system	TXu000870643	21-Aug-98
U.S.	Customer information system-PC	TXu000708795	5-Dec-95